

(10) **Patent No.:** US 9,761,651 B2
(45) **Date of Patent:** Sep. 12, 2017

- U.S. PATENT DOCUMENTS

- FOREIGN PATENT DOCUMENTS

- * cited by examiner

- (74) *Attorney, Agent, or Firm* — Innovation Counsel LLP

- (57) **ABSTRACT**

- A transparent organic light emitting display apparatus include a base substrate, a light blocking pattern disposed on the base substrate, a thin film transistor disposed on the base substrate, a first electrode disposed on the base substrate and electrically connected to the thin film transistor, a pixel defining layer disposed on the base substrate and overlapping the first light blocking pattern, a second electrode disposed on the base substrate, a light emitting structure disposed between the first electrode and the second electrode, and a second light blocking pattern overlapping the first light blocking pattern. The first light blocking pattern defines a first opening. The second light blocking pattern defines a second opening which overlaps the first opening. The pixel defining layer defines a third opening which overlaps the first and second openings configured to pass external light through the first to third openings.

- 20 Claims, 31 Drawing Sheets**

- (58) **Field of Classification Search**
CPC H01L 27/3272; H01L 51/5284; H01L
2227/323; H01L 27/322
USPC 257/40
See application file for complete search history.

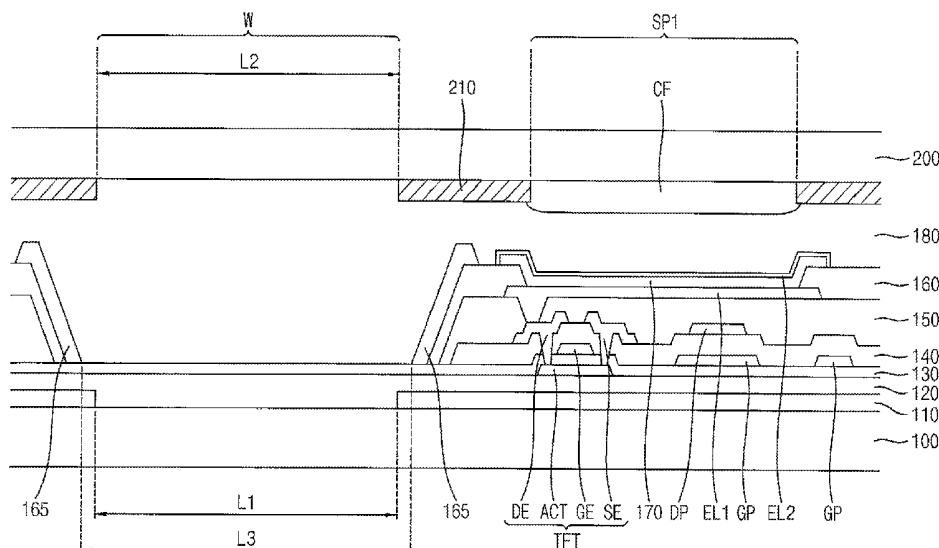


FIG. 1

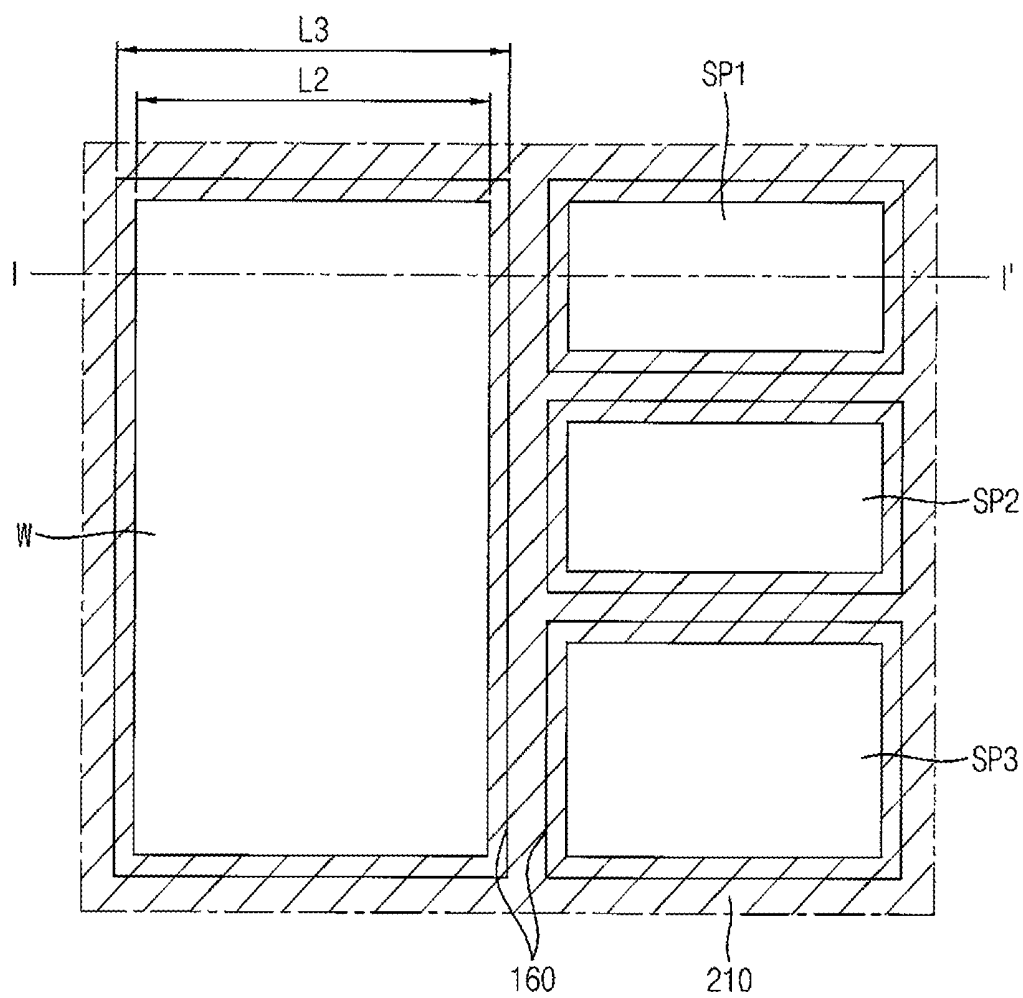


FIG. 3

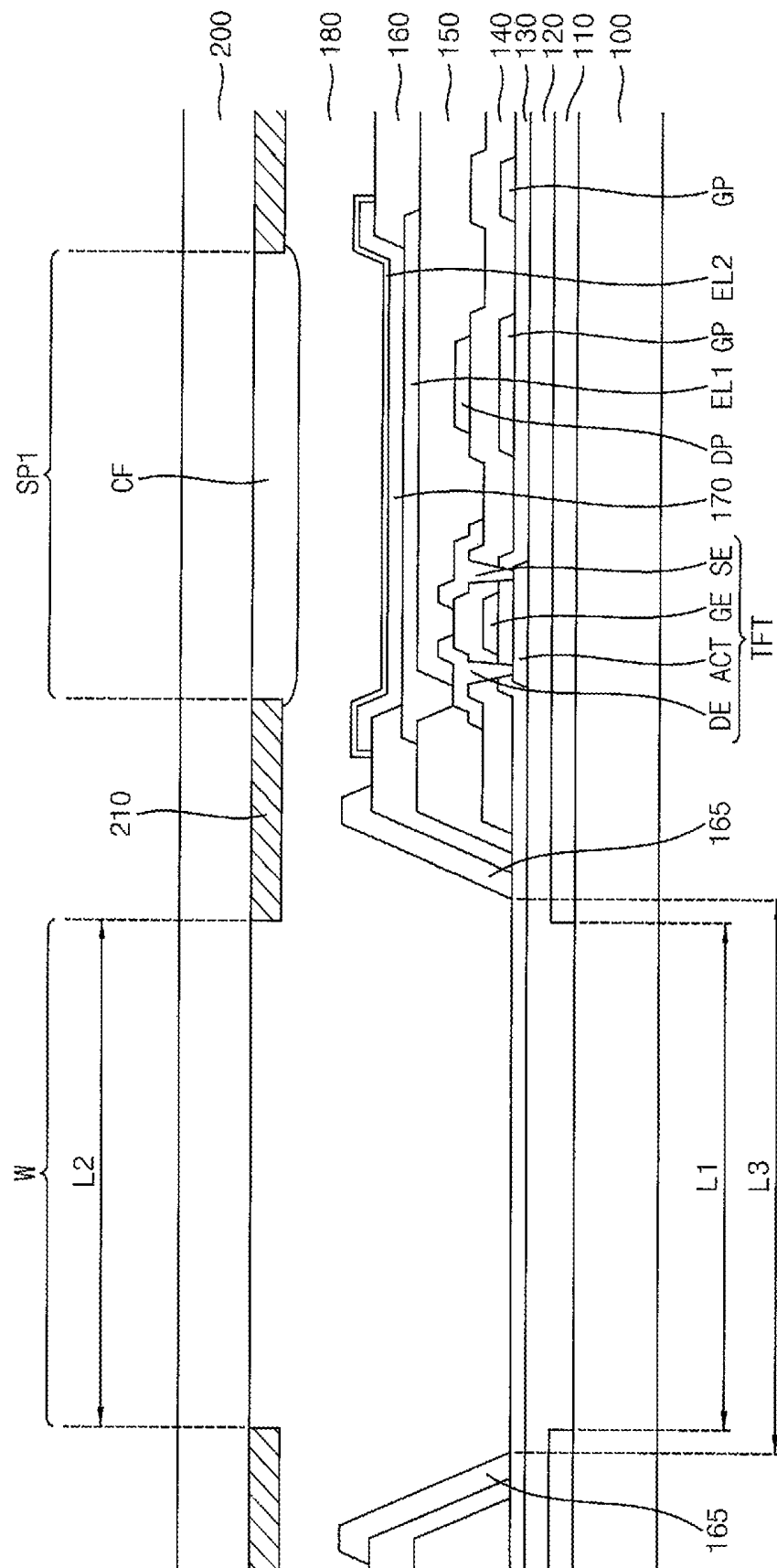


FIG. 5

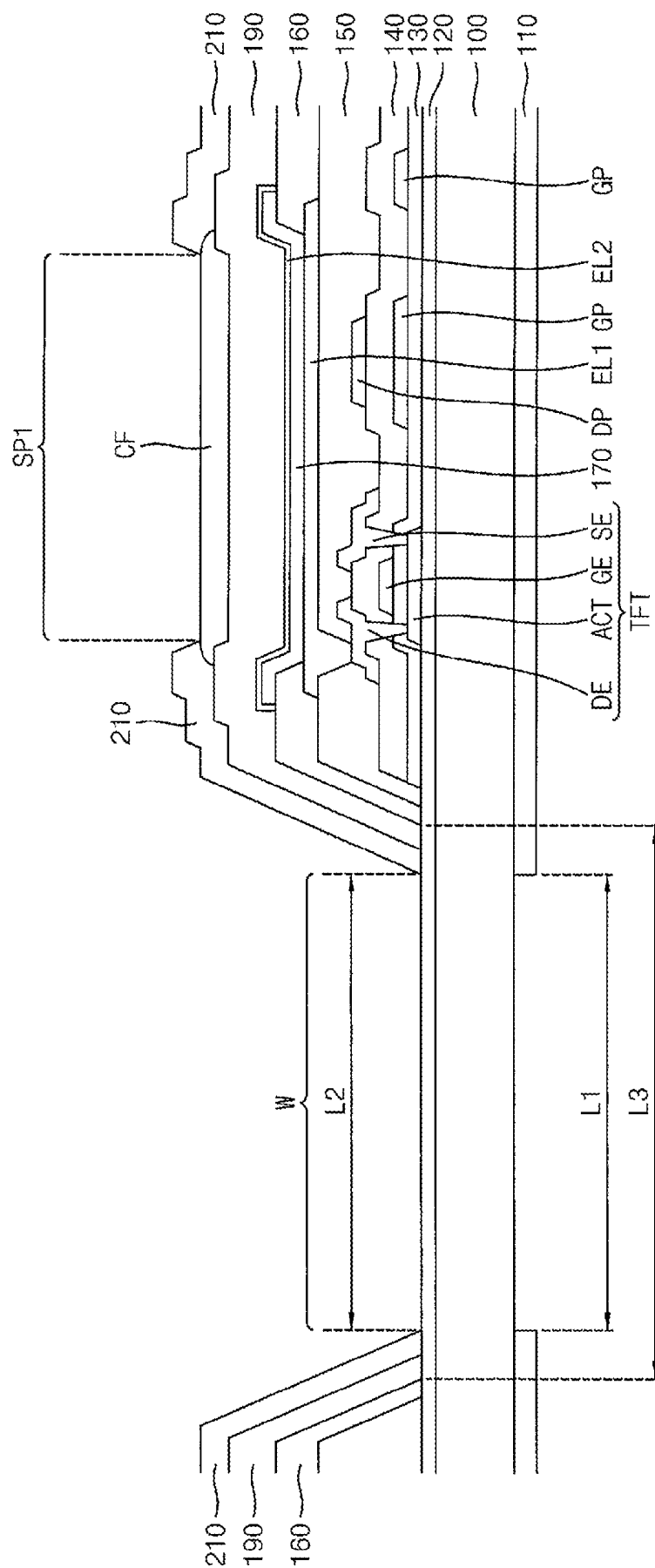


FIG. 6A

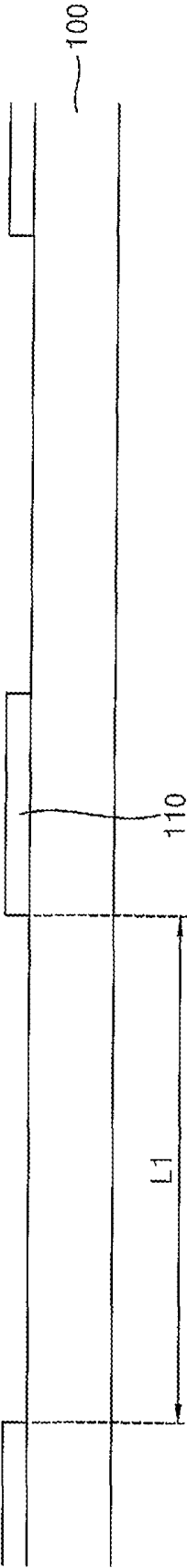


FIG. 6B

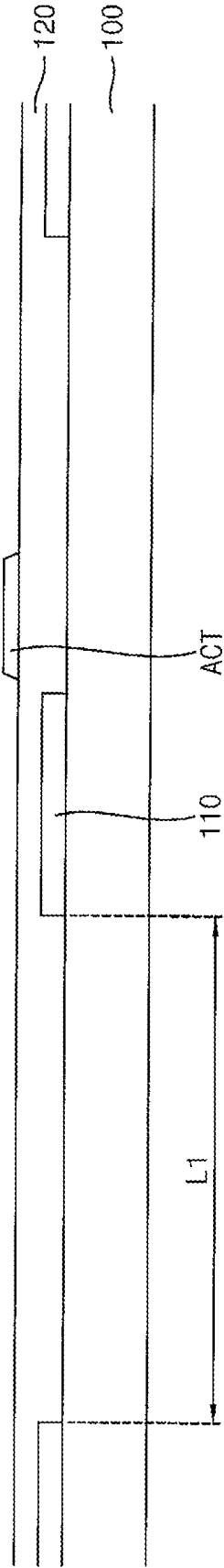


FIG. 6C

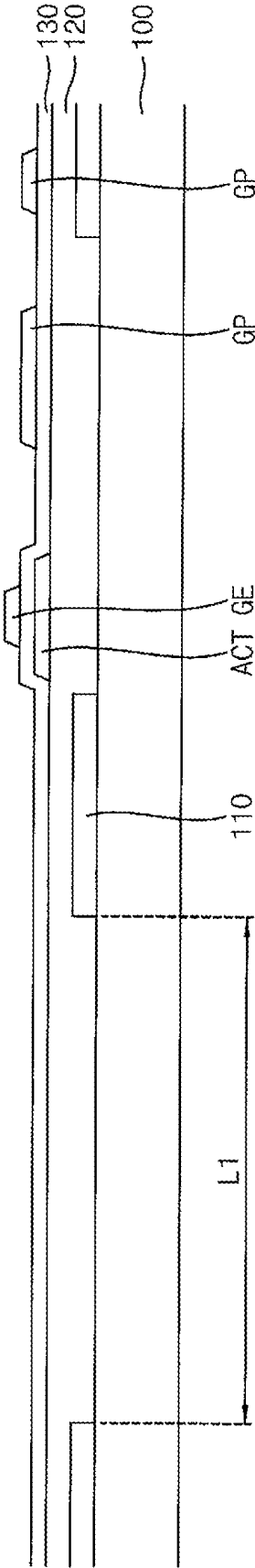


FIG. 6D

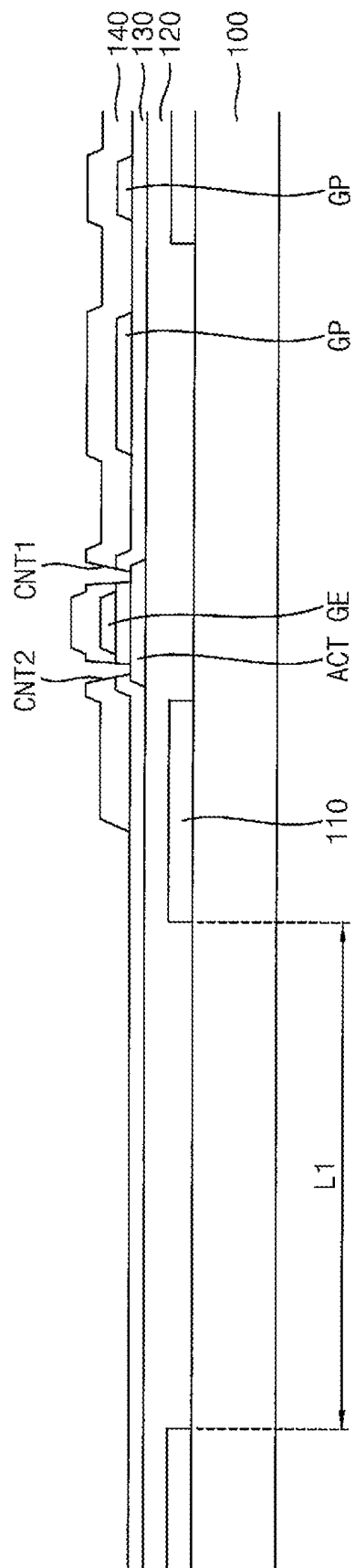


FIG. 6E

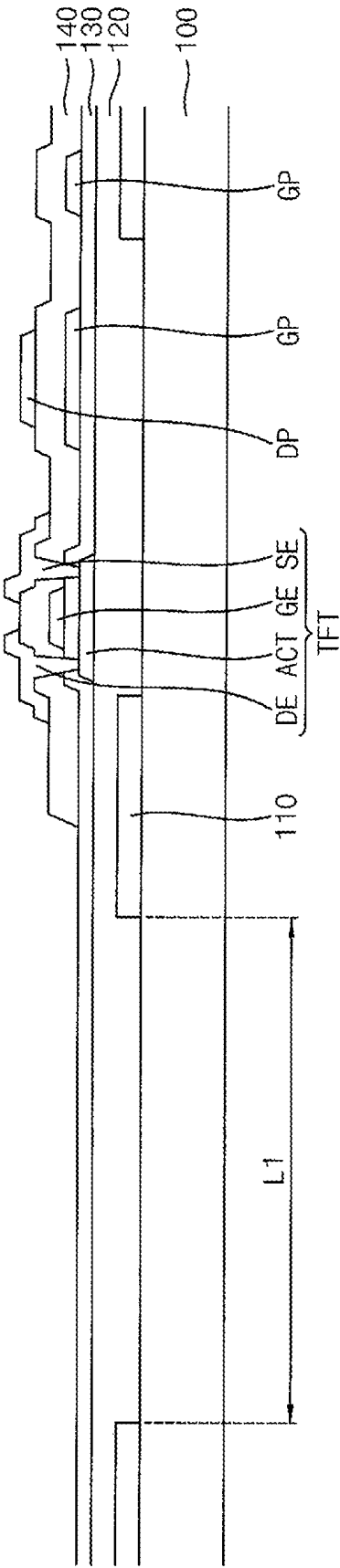


FIG. 6F

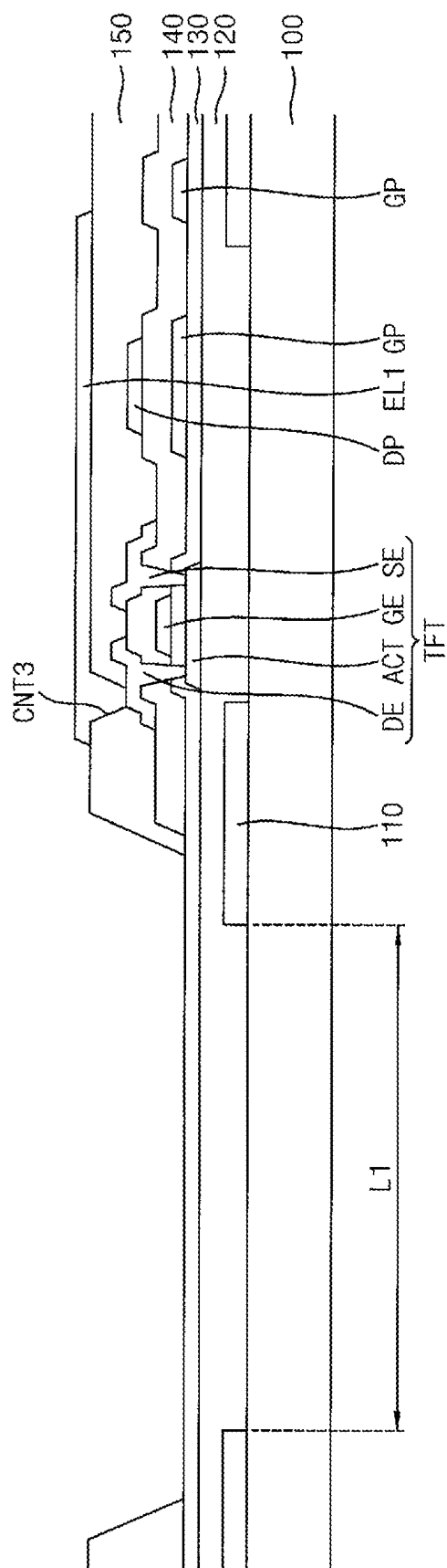


FIG. 6G

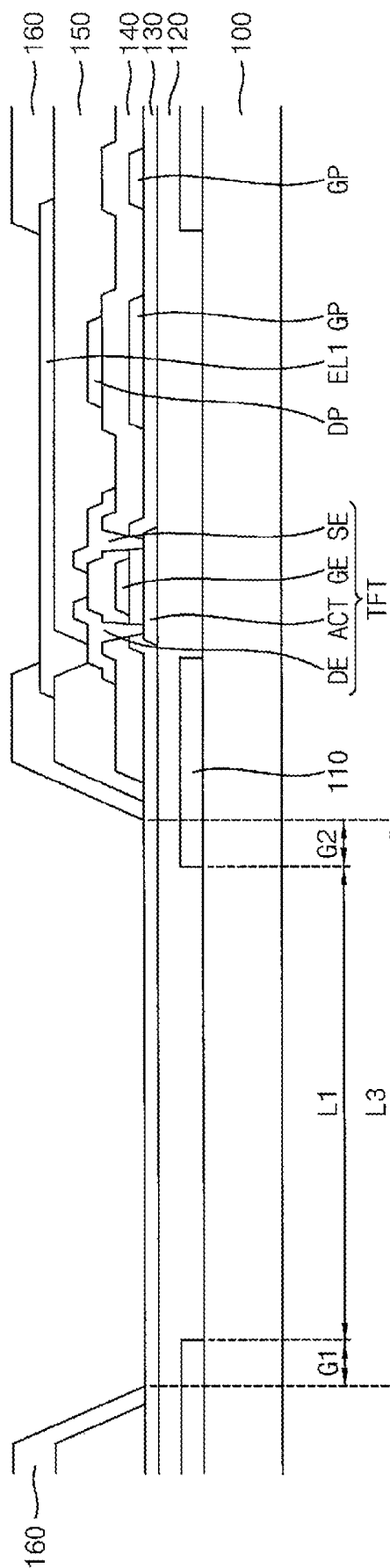


FIG. 6H

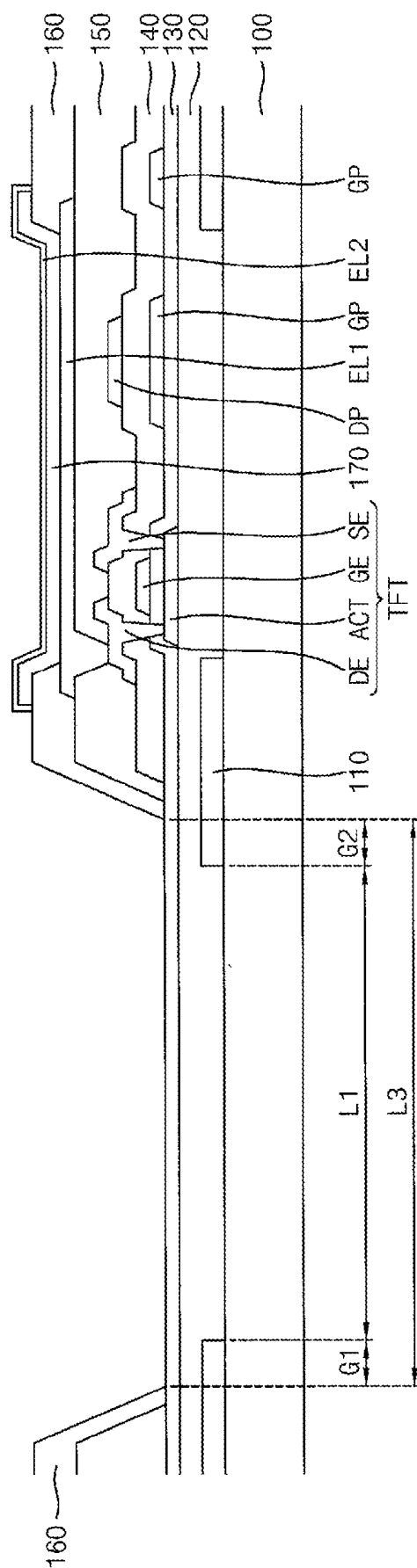


FIG. 6I

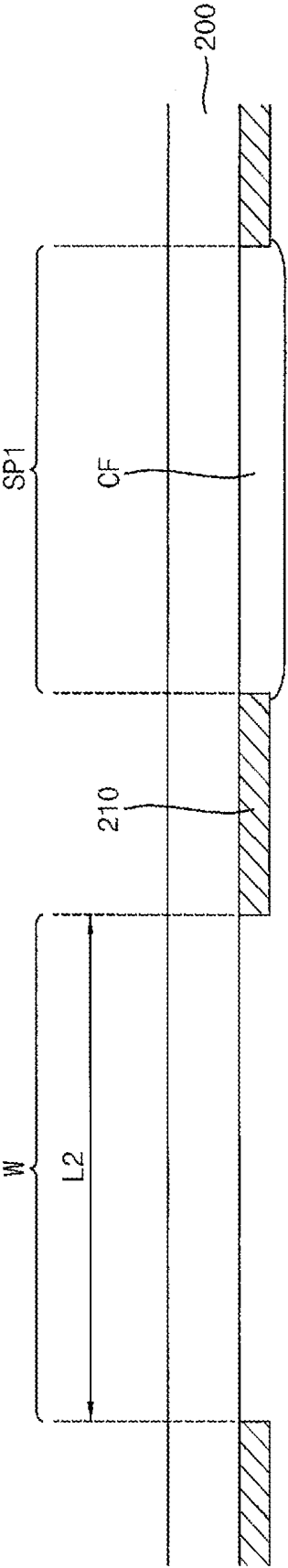


FIG. 6J

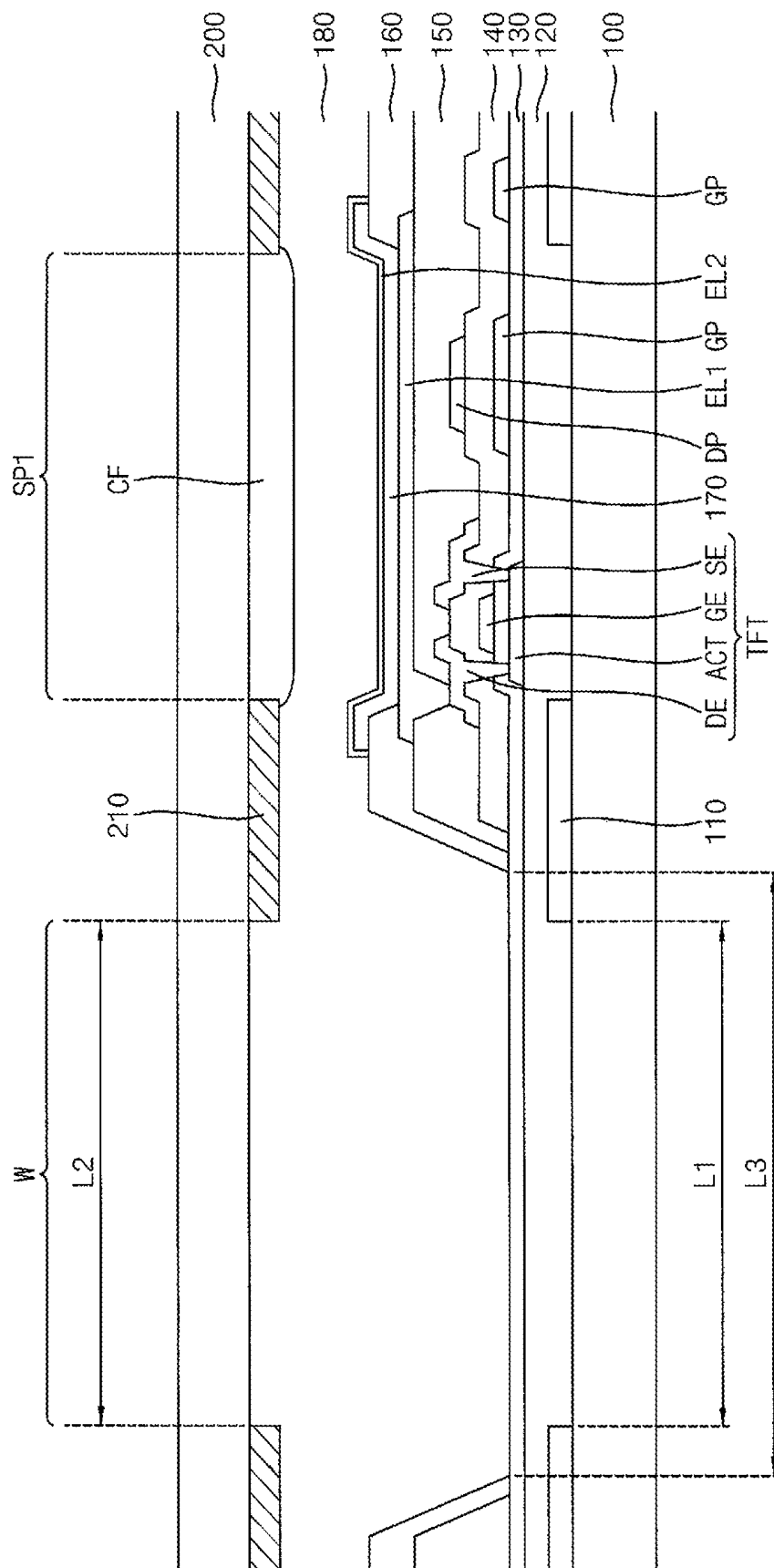


FIG. 7A

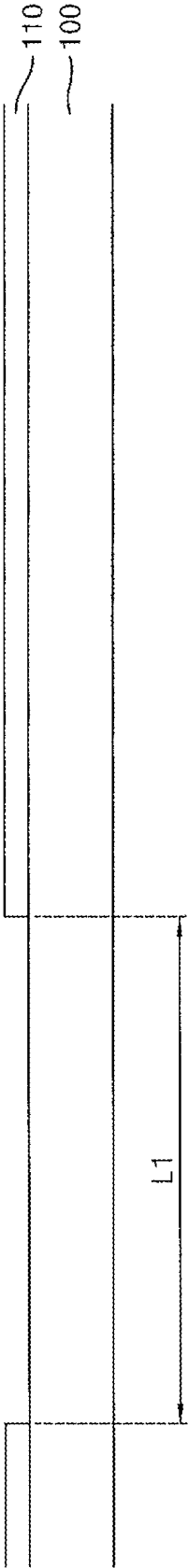


FIG. 7B

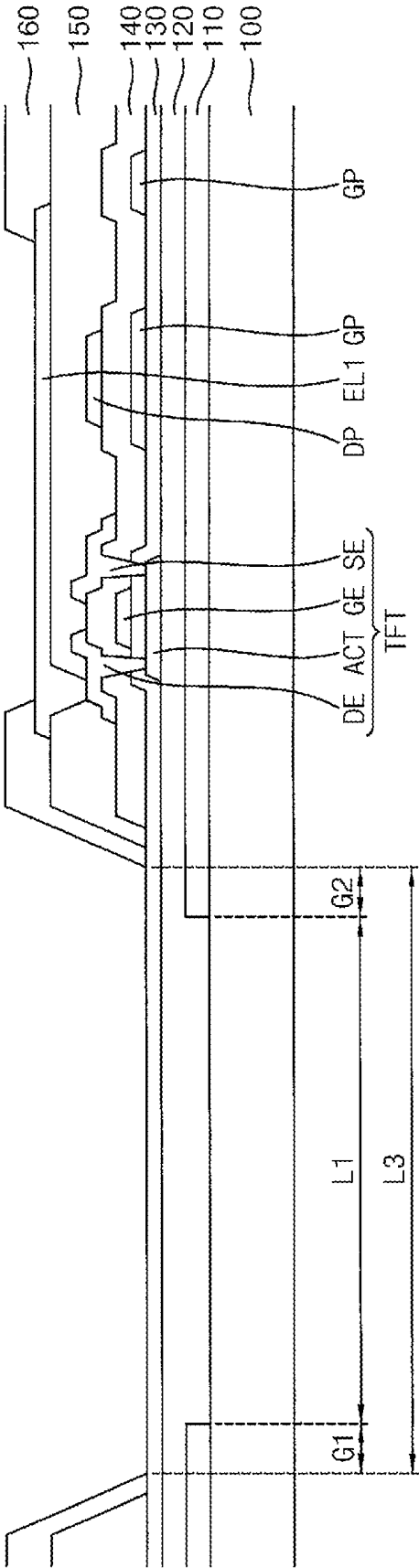


FIG. 7C

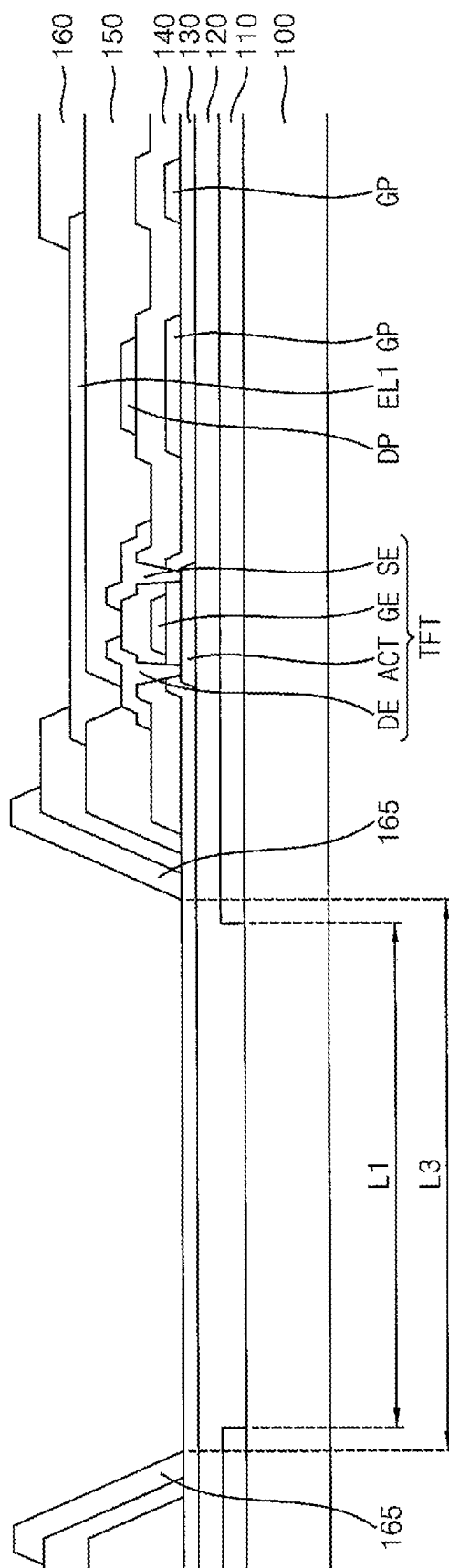


FIG. 7D

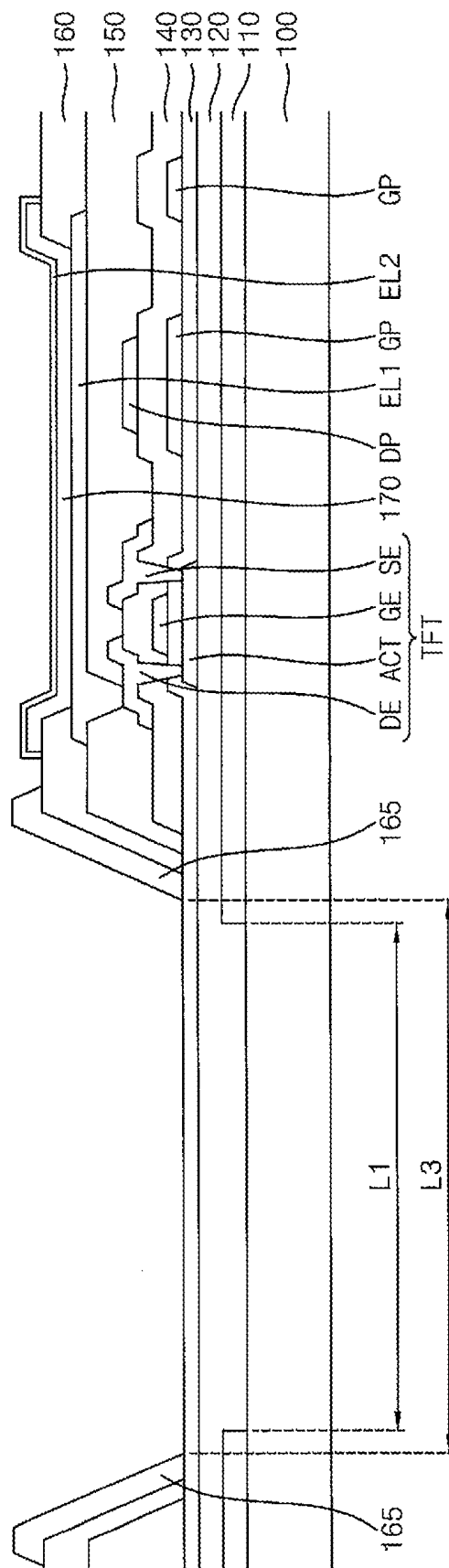


FIG. 7E

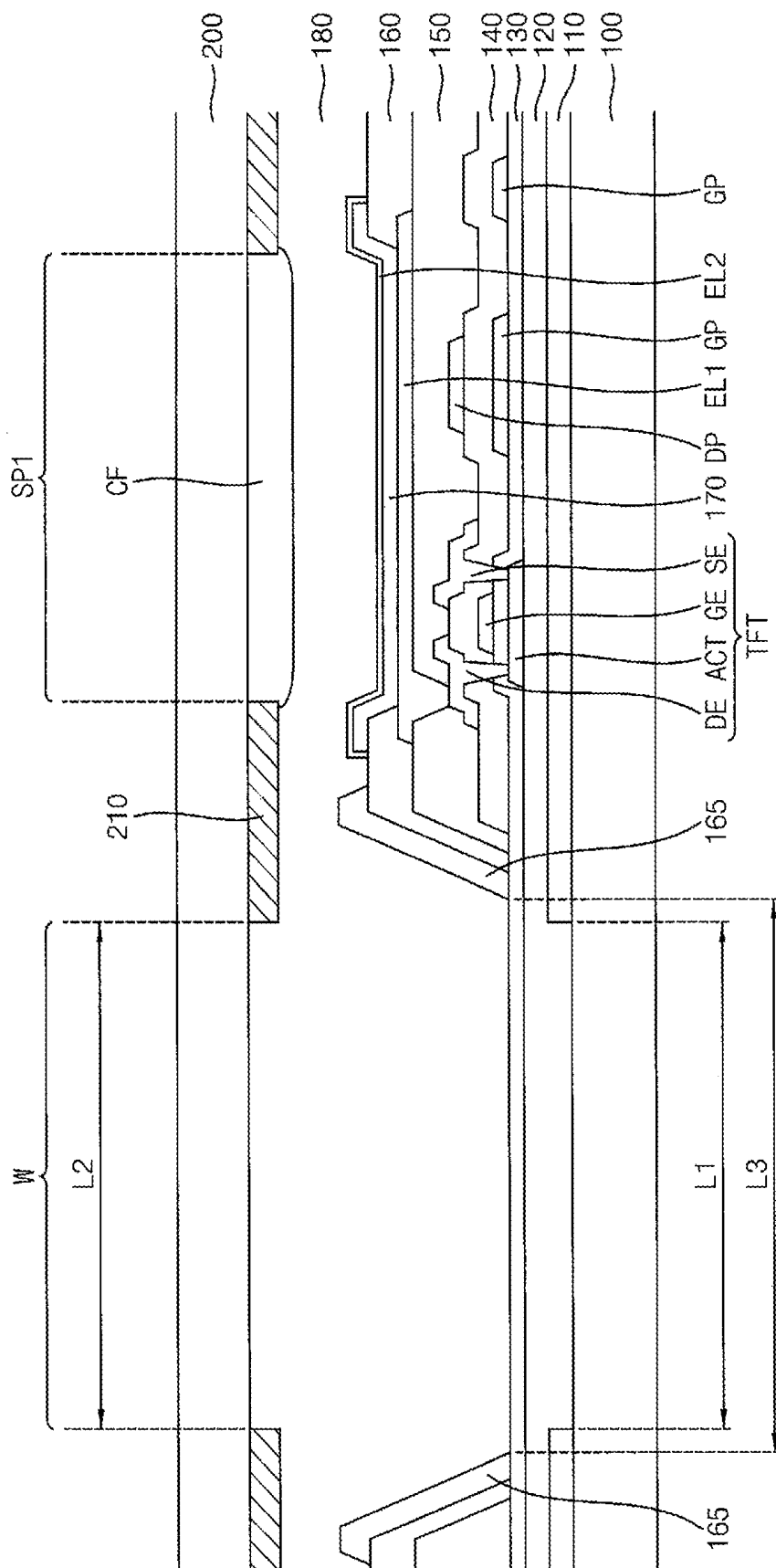


FIG. 8A

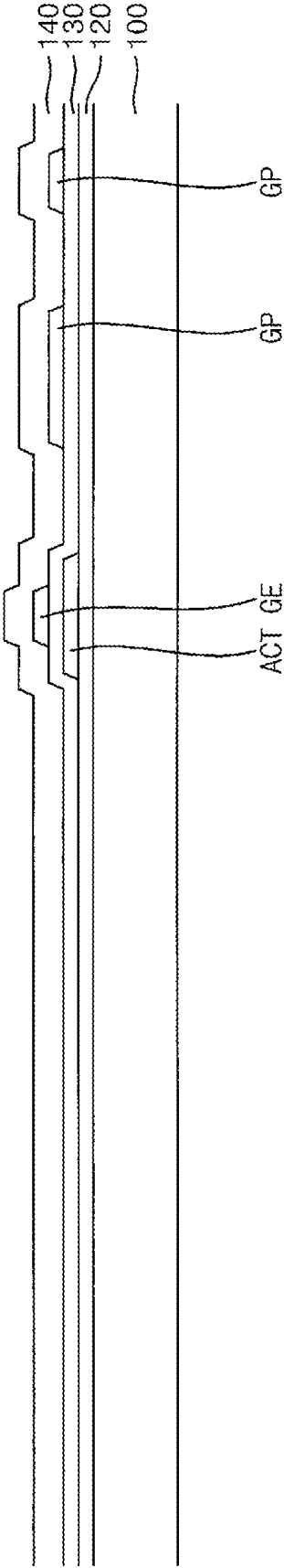


FIG. 8B

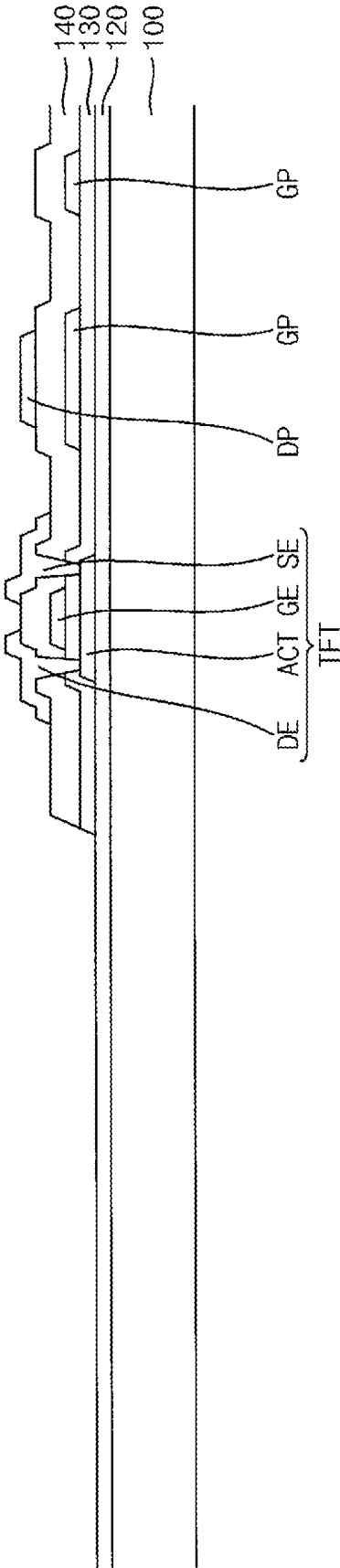


FIG. 8C

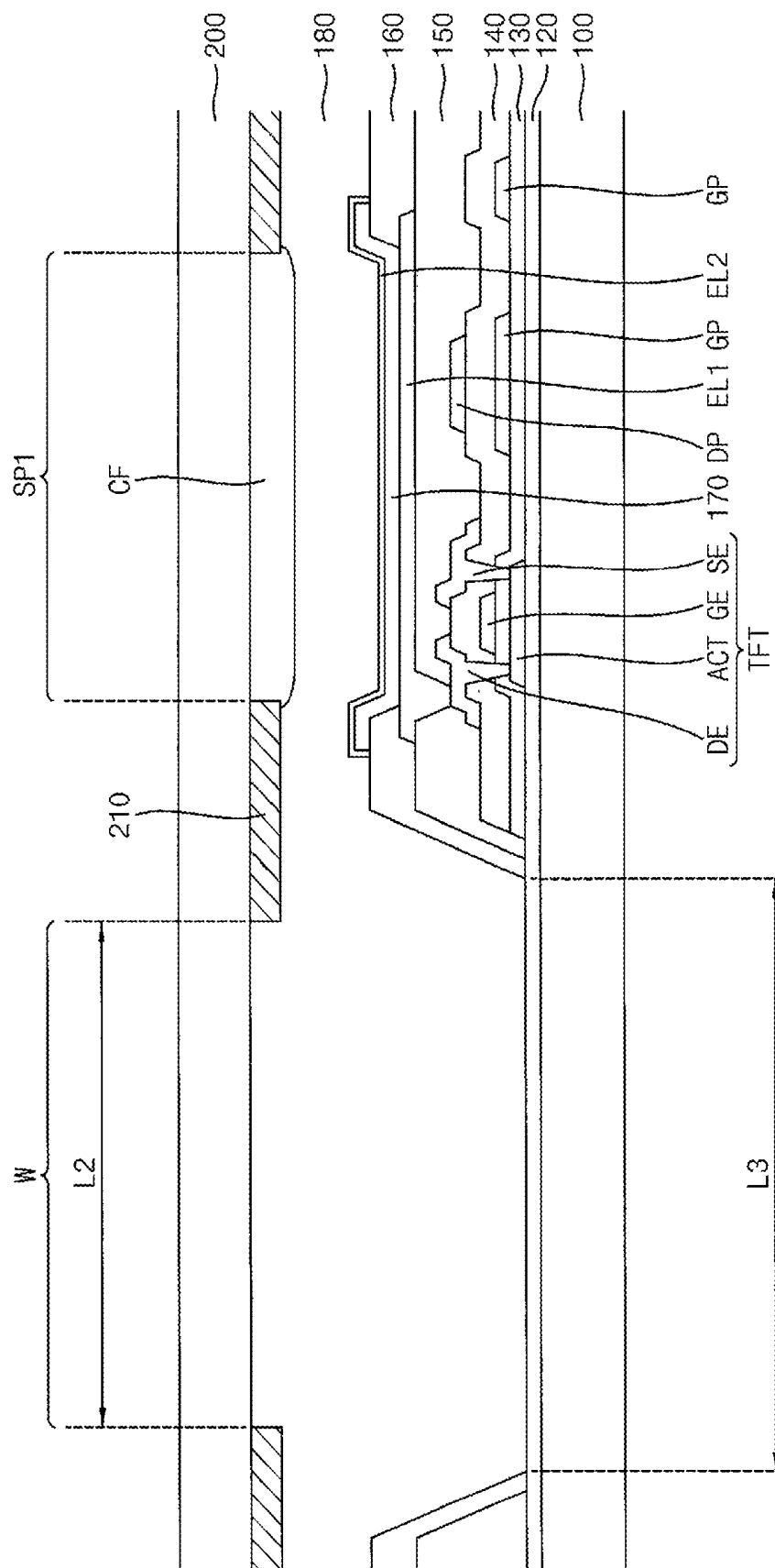


FIG. 8D

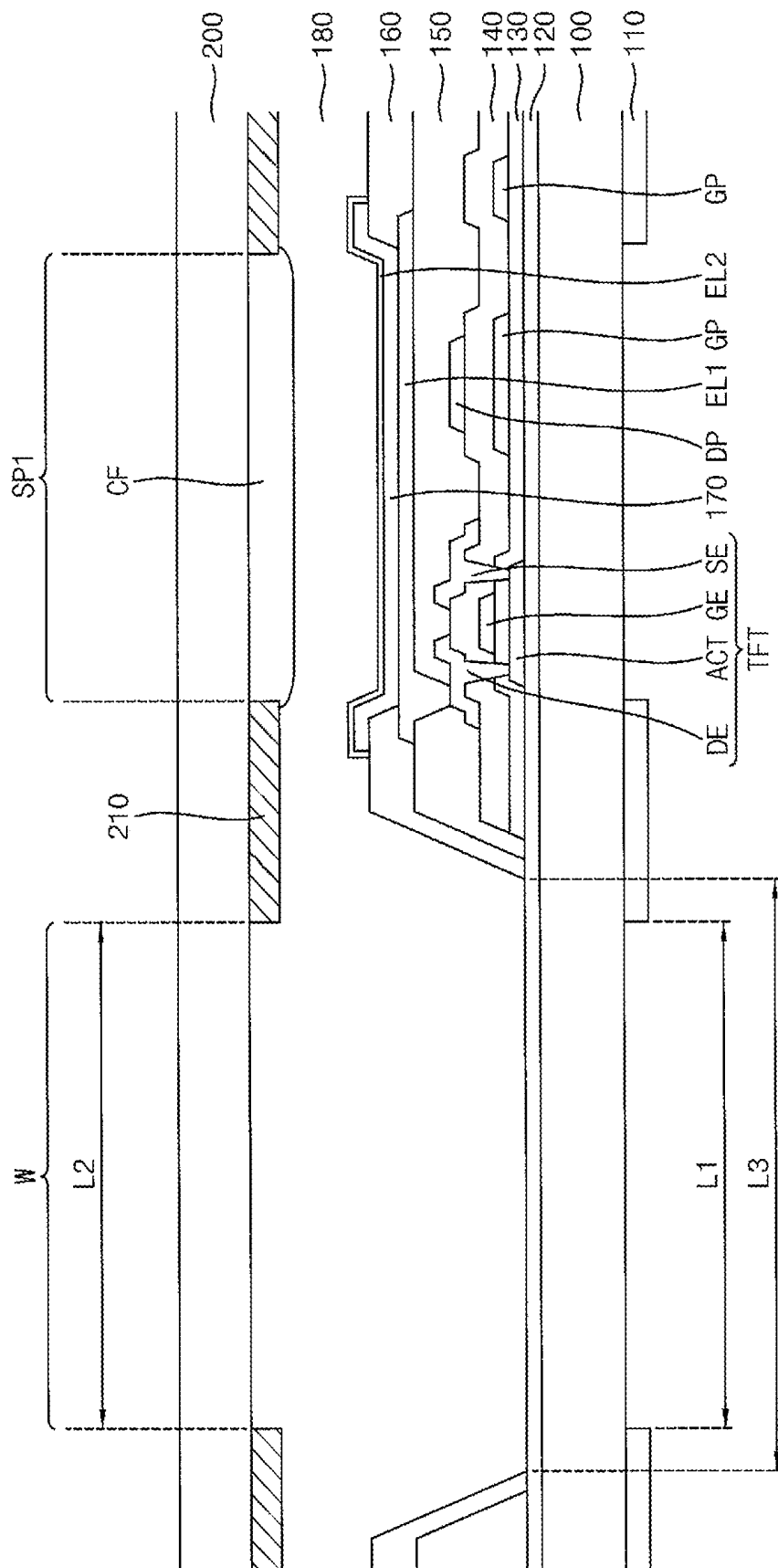


FIG. 9A

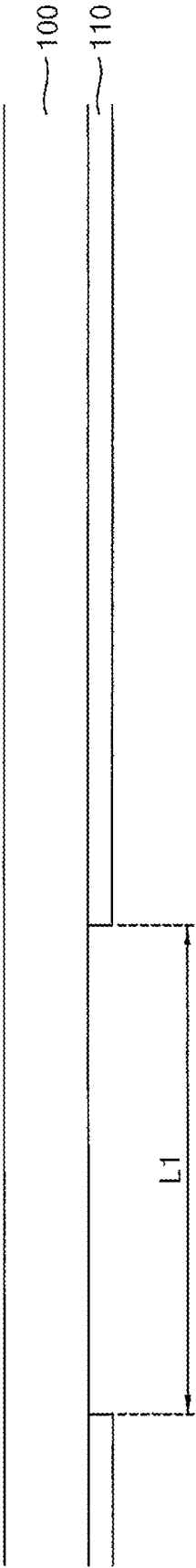


FIG. 9B

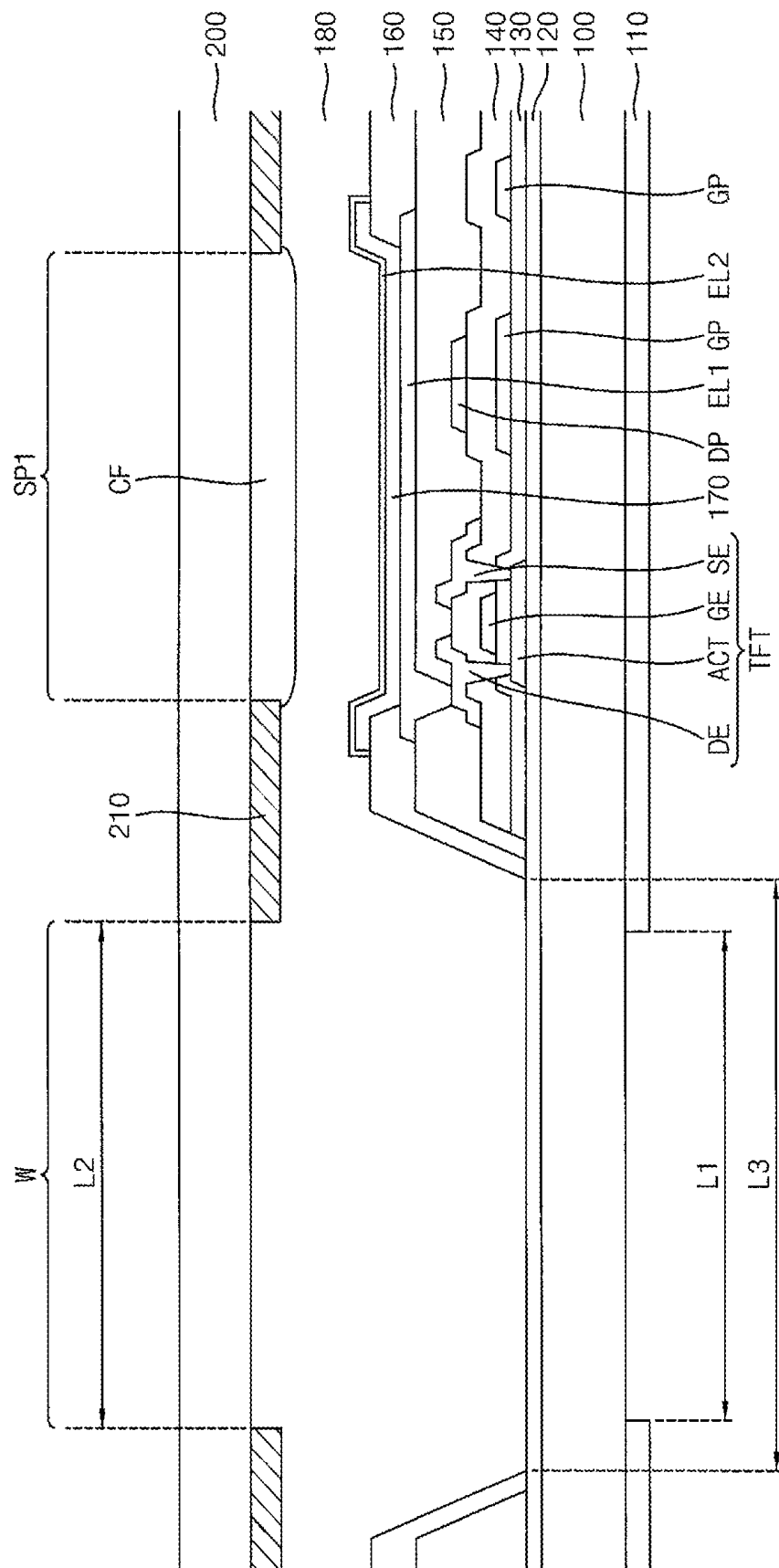


FIG. 10A

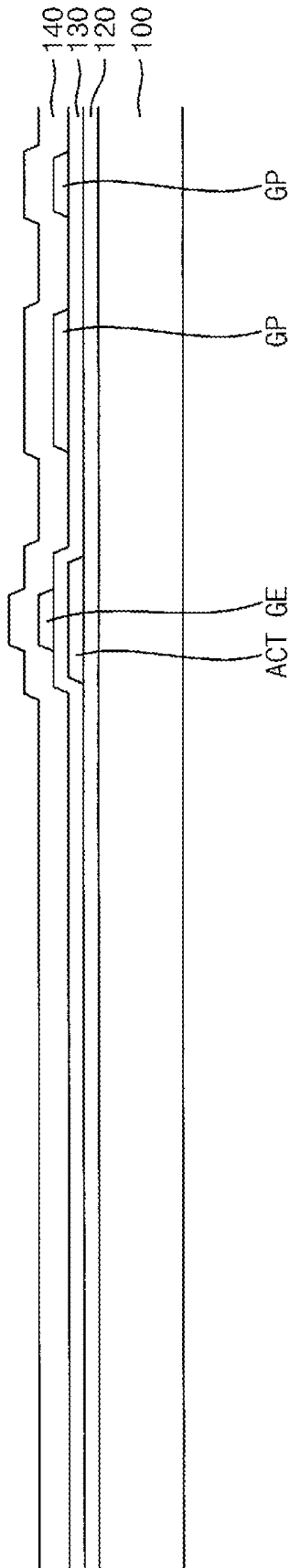


FIG. 10B

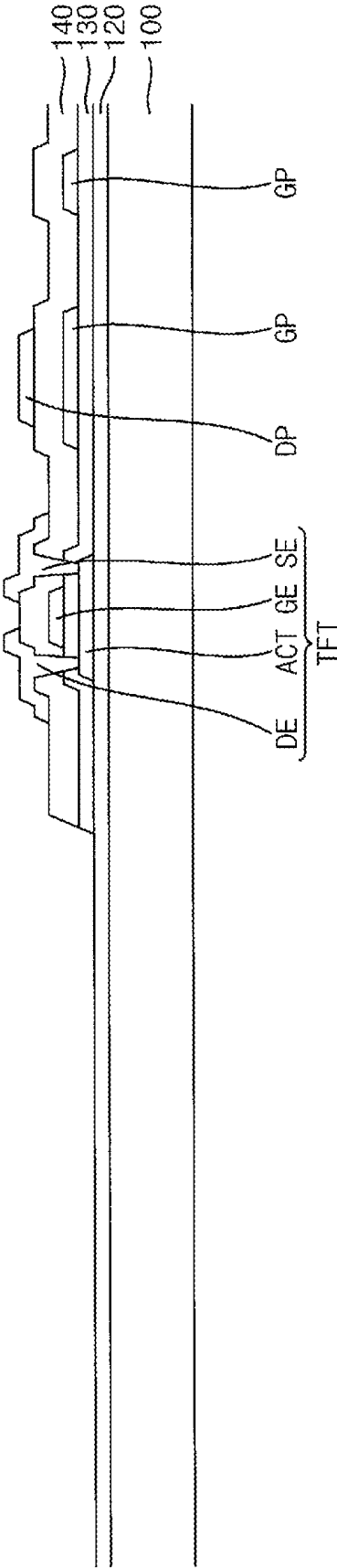


FIG. 10C

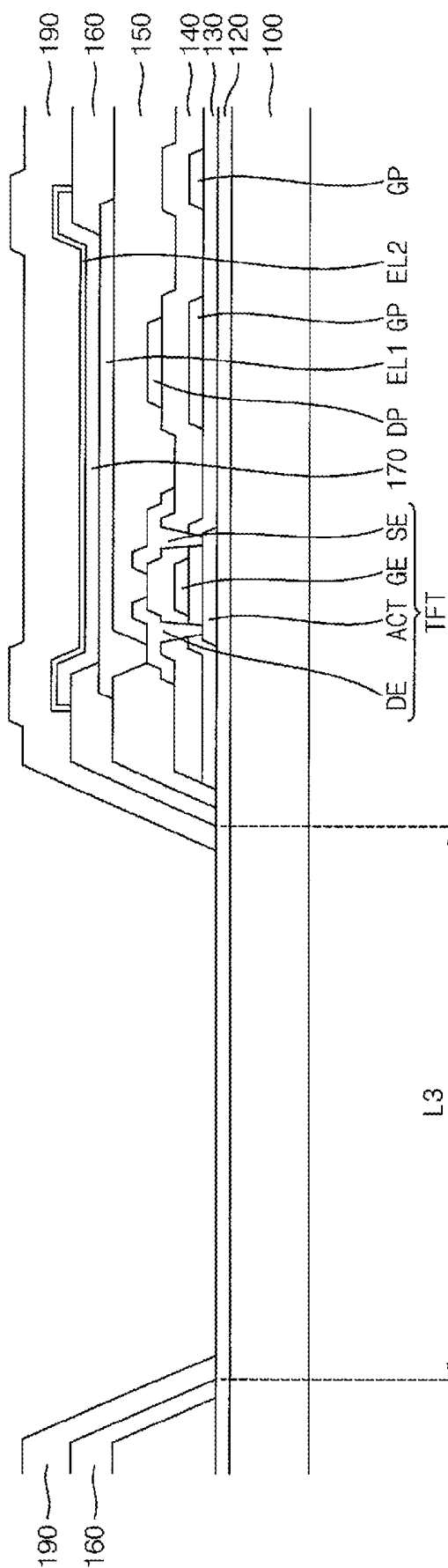


FIG. 10D

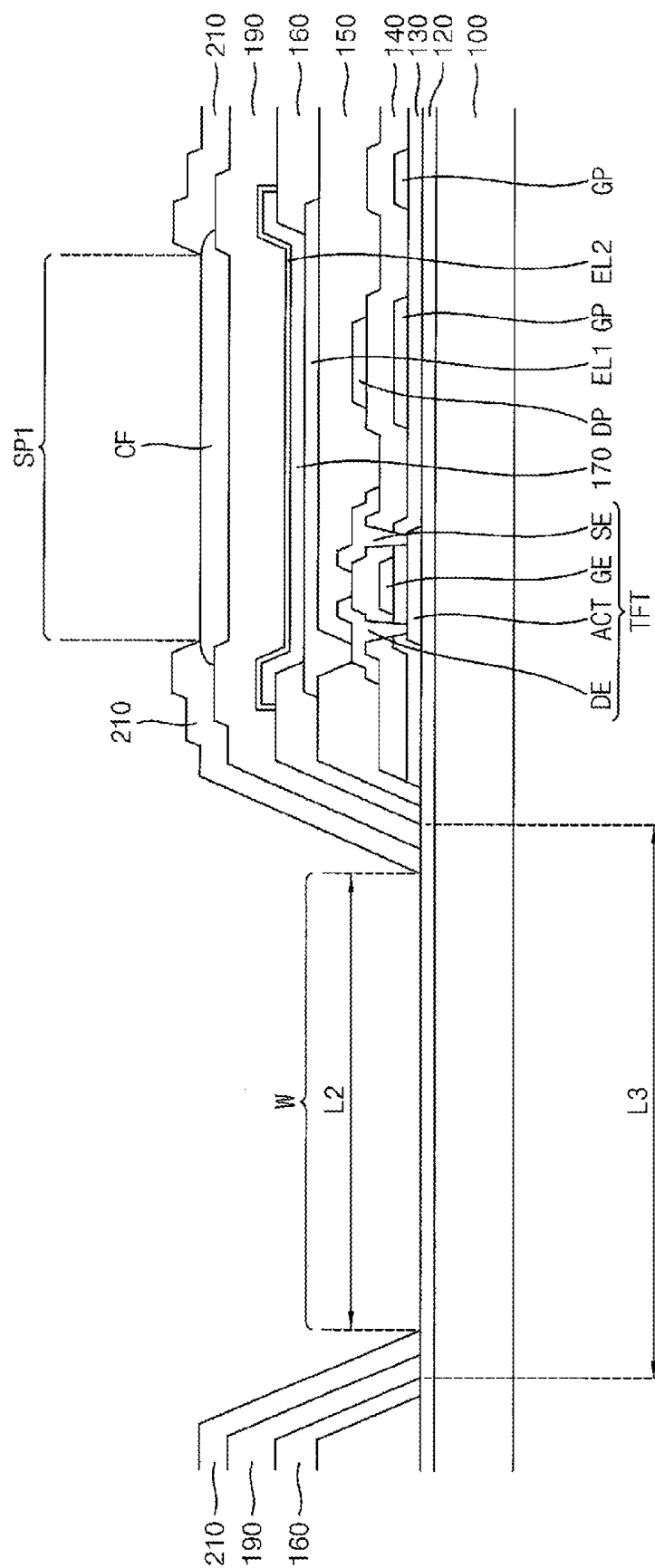
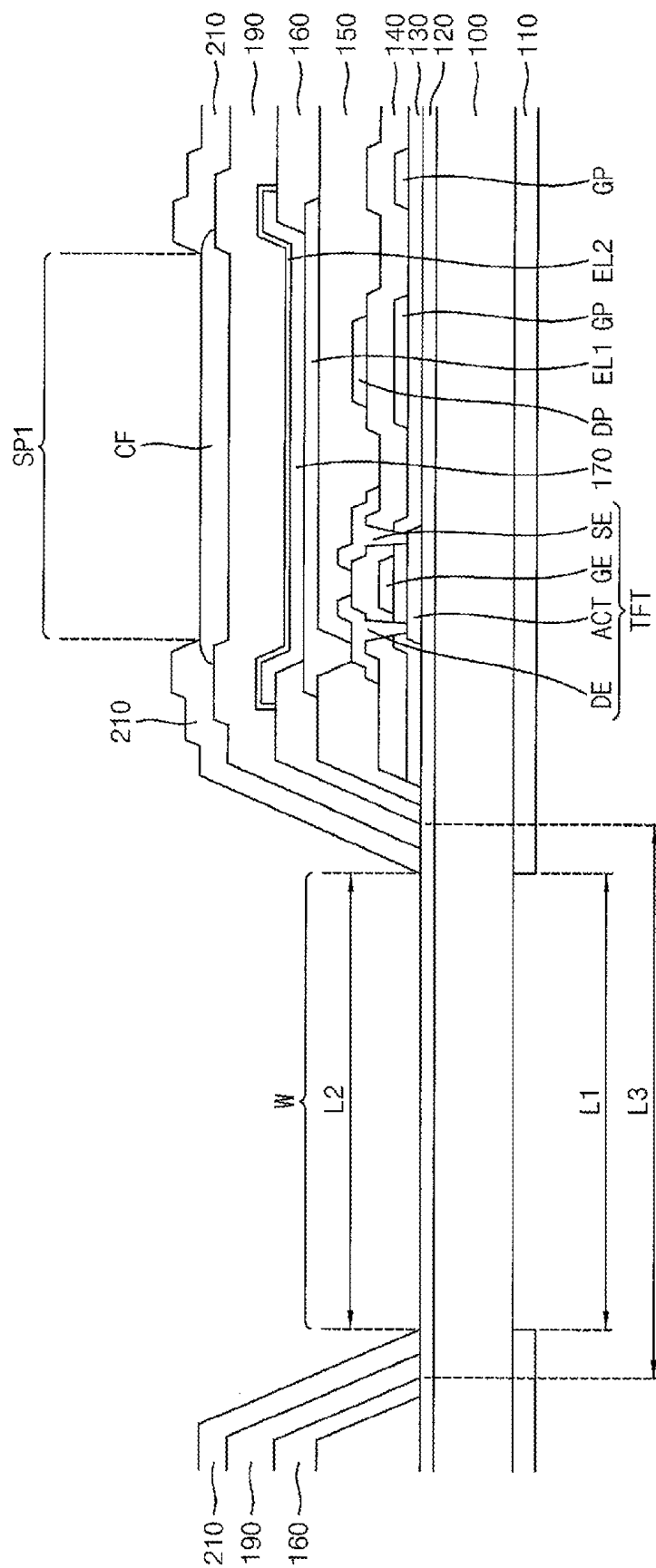


FIG. 10E



TRANSPARENT ORGANIC LIGHT EMITTING DISPLAY APPARATUS AND METHOD OF MANUFACTURING THE SAME

This application claims priority under 35 U.S.C. §119 to Korean Patent Application No. 10-2015-0044741, filed on Mar. 31, 2015, the disclosure of which is incorporated by reference herein in its entirety.

BACKGROUND

1. Field

Example embodiments of the inventive concept relate to a display apparatus and a method of manufacturing the display apparatus. More particularly, example embodiments of the inventive concept relate to a transparent organic light emitting display apparatus and a method of manufacturing the display apparatus.

2. Description of the Related Art

A display device displays an image using a pixel emitting light. An organic light emitting display device includes the pixel having an organic light emitting diode (OLED). The OLED emits the light of which wavelength depends on an organic material included in the OLED. For example, the OLED includes the organic material corresponding to one of a red color light, a green color light, and a blue color light. The organic light emitting display device displays the image by mixing the light emitted by the organic materials.

Recently, a transparent display apparatus which can display an image and pass external light has been actively developed. The transparent display apparatus may transmit the external light, so that users may see an object which is disposed behind the transparent display apparatus.

Here, elements disposed near a transparent window may cause reflection of the external light, so that sharpness of a transmitted image may be decreased.

SUMMARY

Example embodiments provide a transparent organic light emitting display apparatus capable of improving sharpness of a transmitted image.

Example embodiments also provide a method of manufacturing the transparent organic light emitting display apparatus.

According to some example embodiments, a transparent organic light emitting display apparatus include a base substrate, a light blocking pattern disposed on the base substrate, a thin film transistor disposed on the base substrate, a first electrode disposed on the base substrate and electrically connected to the thin film transistor, a pixel defining layer disposed on the base substrate and overlapping the first light blocking pattern, a second electrode disposed on the base substrate, a light emitting structure disposed between the first electrode and the second electrode, and a second light blocking pattern overlapping the first light blocking pattern. The first light blocking pattern defines a first opening. The second light blocking pattern defines a second opening which overlaps the first opening. The pixel defining layer defines a third opening which overlaps the first and second openings configured to pass external light through the first to third openings.

In example embodiments, a width of the first opening may be smaller than a width of the third opening. A width of the second opening may be smaller than a width of the third opening.

In example embodiments, the width of the first opening may be substantially same as the width of the second opening.

In example embodiments, a gap between a boundary of the first opening and a boundary of the third opening may be about 1 μm to about 5 μm in a plan view. A gap between a boundary of the second opening and a boundary of the third opening may be about 1 μm to about 5 μm in a plan view.

In example embodiments, the gap between the boundary of the first opening and the boundary of the third opening may be uniform.

In example embodiments, the first light blocking pattern may be disposed opposite to the thin film transistor with respect to the base substrate.

In example embodiments, the transparent organic light emitting display apparatus may further include a third light blocking pattern disposed on the pixel defining layer and spaced apart from the light emitting structure. The third light blocking pattern may define a fourth opening which covers a boundary of the third opening and overlap the first and second openings.

In example embodiments, a width of the first opening may be smaller than a width of the fourth opening. A width of the second opening may be smaller than a width of the fourth opening.

In example embodiments, the transparent organic light emitting display apparatus may further include a color filter disposed on the second electrode. The second light blocking pattern may make contact with the color filter.

In example embodiments, the transparent organic light emitting display apparatus may further include a sealing substrate. The color filter and the second light blocking pattern may be disposed on the sealing substrate.

In example embodiments, the transparent organic light emitting display apparatus may further include a buffer layer covering the base substrate. The buffer layer may be disposed between the base substrate and the thin film transistor. The first light blocking pattern may be disposed between the buffer layer and the base substrate.

In example embodiments, the transparent organic light emitting display apparatus may further include a first insulation layer disposed on the buffer layer and a second insulation layer disposed on the first insulation layer. The first and second insulation layers may define an opening where the first to third openings are overlapped each other.

In example embodiments, the transparent organic light emitting display apparatus may further include a thin film encapsulation layer including a plurality of organic films and inorganic films which are alternately stacked, and a color filter disposed on the thin film encapsulation layer and overlapping the light emitting structure. The second light blocking pattern may be disposed on the thin film encapsulation layer and configured to expose the color filter.

In example embodiments, the first light blocking pattern may make contact with the base substrate.

According to some example embodiments, a method of manufacturing a transparent organic light emitting display apparatus include forming a first light blocking pattern on a base substrate, forming a thin film transistor on the base substrate, forming a pixel defining layer on the base substrate on which the thin film transistor is formed, forming a light emitting structure on the base substrate on which the pixel defining layer is formed, and forming a second light blocking pattern overlapping the pixel defining layer. The first light blocking pattern defines a first opening. The second light blocking pattern defines a second opening which overlaps the first opening. The pixel defining layer

defines a third opening which overlaps the first and second openings. The first to third openings are configured to pass external light therethrough.

In example embodiments, the method may further include forming a third light blocking pattern on the pixel defining layer before forming the light emitting structure. The third light blocking pattern may be spaced apart from the light emitting structure.

In example embodiments, the method may further include a color filter overlapping the light emitting structure before forming the second light blocking pattern.

In example embodiments, the method may further include forming a buffer layer on the base substrate on which the first light blocking pattern is formed before forming the thin film transistor.

In example embodiments, the first light blocking pattern may be formed by attaching a light blocking film on the base substrate.

According to some example embodiments, a transparent organic light emitting display apparatus includes a transparent window configured to pass external light therethrough and a pixel configured to display an image. The transparent organic light emitting display apparatus includes a first light blocking pattern defining a first opening corresponding to the transparent window, a second light blocking pattern overlapping the first light blocking pattern, and an opaque elements disposed between the first light blocking pattern and the second light blocking pattern. The second light blocking pattern defines a second opening overlapping the first opening. The opaque elements define a third opening overlapping the first opening and the second opening. The third opening is substantially larger than the first opening and the second opening.

Therefore, a transparent organic light emitting display apparatus may include a pixel defining layer, a first light blocking pattern and a second light blocking pattern. A boundary of the pixel defining layer may be covered by the first light blocking pattern and the second light blocking pattern, so that reflection of external light passing a transparent window by elements of the transparent organic light emitting display apparatus may be decreased. Thus, quality of a transmitted image by the external light may be improved.

In addition, the transparent organic light emitting display apparatus may include a third light blocking pattern disposed on boundary side surfaces of an opening of the pixel defining layer which corresponds to the transparent window. Reflection of external light passing the transparent window by the elements of the transparent organic light emitting display apparatus may be decreased by the first to third light blocking patterns. Thus, quality of a transmitted image by the external light may be improved.

BRIEF DESCRIPTION OF THE DRAWINGS

The above and other features of the inventive concept will become more apparent by describing in detail example embodiments thereof with reference to the accompanying drawings, in which:

FIG. 1 is a plan view illustrating a pixel of a transparent organic light emitting display apparatus according to an example embodiment of the inventive concept;

FIG. 2 is a cross-sectional view taken along a line I-I' of FIG. 1;

FIG. 3 is a cross-sectional view illustrating a transparent organic light emitting display apparatus according to an example embodiment of the inventive concept;

FIG. 4 is a cross-sectional view illustrating a transparent organic light emitting display apparatus according to an example embodiment of the inventive concept;

FIG. 5 is a cross-sectional view illustrating a transparent organic light emitting display apparatus according to an example embodiment of the inventive concept;

FIGS. 6A, 6B, 6C, 6D, 6E, 6F, 6G 6H, 6I and 6J are cross-sectional views illustrating a method of manufacturing the transparent organic light emitting display apparatus of FIG. 2;

FIGS. 7A, 7B, 7C, 7D and 7E are cross-sectional views illustrating a method of manufacturing the transparent organic light emitting display apparatus of FIG. 3;

FIGS. 8A, 8B, 8C and 8D are cross-sectional views illustrating a method of manufacturing the transparent organic light emitting display apparatus of FIG. 4;

FIGS. 9A and 9B are cross-sectional views illustrating another method of manufacturing the transparent organic light emitting display apparatus of FIG. 4; and

FIGS. 10A, 10B, 10C, 10D and 10E are cross-sectional views illustrating a method of manufacturing the transparent organic light emitting display apparatus of FIG. 5.

DETAILED DESCRIPTION

Hereinafter, the inventive concept will be explained in detail with reference to the accompanying drawings.

FIG. 1 is a plan view illustrating a pixel of a transparent organic light emitting display apparatus according to an example embodiment of the inventive concept.

Referring to FIG. 1, the transparent organic light emitting display apparatus may include a plurality of pixels. Each of plurality of pixels may include a transparent window W and a plurality of sub-pixels. According to the present example embodiment, each of the plurality of pixels of the transparent organic light emitting display apparatus may include the transparent window W, a first sub-pixel SP1, a second sub-pixel SP2 and a third sub-pixel SP3.

Each of the first to third light emitting portions (refers to 170 of FIG. 2) may be disposed corresponding to each of the first to third sub-pixels SP1 to SP3, respectively.

The first light emitting portion, the second light emitting portion and the third light emitting portion may emit lights having different colors according to driving of the pixels of the transparent organic light emitting display apparatus. For example, the first light emitting portion may emit red light, the second light emitting portion may emit green light, and the third light emitting portion may emit blue light.

The transparent window W may pass external light, so that users may see an object behind the transparent organic light emitting display apparatus through the transparent window W.

A pixel defining layer 160 is disposed on a first base substrate 100. A second light blocking pattern 210 (painted in gray) which is disposed on a second base substrate 200 may define the transparent window W and the first to third sub-pixels SP1 to SP3. Thus, an opening formed through the second light blocking pattern 210 may define the transparent window W, and the opening may have a width which is second length L2 in a first direction.

An opening formed through the pixel defining layer 160 may have a width which is a third length L3 in the first direction.

The second length L2 may be smaller than the third length L3. Thus, the opening formed through the second light blocking pattern 210 may be smaller than the opening formed through the pixel defining layer 160 in the first

direction. The opening formed through the second light blocking pattern **210** may be smaller than the opening formed through the pixel defining layer **160** in the second direction. The second direction may be substantially perpendicular to the first direction.

Accordingly, a boundary of the pixel defining layer **160** may be covered by the second light blocking pattern **210**. Thus, reflection of the external light, which passes the transparent window **W**, due to elements of the transparent organic light emitting display apparatus may be decreased, so that quality of a transmitted image by the external light may be improved.

In addition, an opening formed through a first light blocking pattern **110** disposed on the first base substrate **100** (refers to **110** of FIG. 2) may define the transparent window **W**, and the opening may have a width which is first length (refers to **L1** of FIG. 2) in the first direction.

The first length **L1** may be smaller than the third length **L3**. Thus, the opening formed through the first light blocking pattern may be smaller than the opening formed through the pixel defining layer **160**. The opening formed through the first light blocking pattern **110** may have a shape substantially same as the opening formed through the second light blocking pattern **210**. In addition, in consideration of the alignment error between the first base substrate **100** and the second base substrate **200**, the opening formed through the second light blocking pattern **210** may be smaller than the opening formed through the first light blocking pattern **110**. Contrary, the opening formed through the first light blocking pattern may be smaller than the opening formed through the second light blocking pattern **210**.

Accordingly, the boundary of the pixel defining layer **160** may be covered by the first light blocking pattern. Thus, reflection of the external light, which passes the transparent window **W**, due to elements of the transparent organic light emitting display apparatus may be decreased, so that quality of a transmitted image by the external light may be improved. Although the pixel includes the transparent window **W** and sub-pixels in the present example embodiment, it is not to be construed as limited to this specific example embodiment. In one example embodiment, a pixel may include a plurality of transparent windows and a plurality of sub-pixels. In one example embodiment, a transparent window of a pixel may be connected to a transparent window of adjacent pixel.

FIG. 2 is a cross-sectional view taken along a line I-I' of FIG. 1.

Referring to FIG. 2, the transparent organic light emitting display apparatus may include a base substrate **100**, a first light blocking pattern **110**, a buffer layer **120**, a thin film transistor TFT, a first insulation layer **130**, a gate pattern GP, a second insulation layer **140**, a data pattern DP, a third insulation layer **150**, a first electrode **EL1**, a pixel defining layer **160**, a light emitting structure **170**, a second electrode **EL2**, a sealing substrate **200**, a second light blocking layer **210**, and a color filter CF.

The base substrate **100** may include a transparent insulation substrate. For example, the base substrate **100** may include a glass substrate, a quartz substrate, a transparent resin substrate, etc. Examples of the transparent resin substrate for the base substrate **100** may include polyimide-based resin, acryl-based resin, polyacrylate-based resin, polycarbonate-based resin, polyether-based resin, sulfonic acid containing resin, polyethyleneterephthalate-based resin, etc.

The first light blocking pattern **110** may be disposed on the base substrate **100**. The first light blocking pattern **110**

may block light. The first light blocking pattern **110** may include organic material or inorganic material which can block light. For example, the first light blocking pattern **110** may be a black matrix pattern including chrome.

The first light blocking pattern **110** may define an opening corresponding to a transparent window **W**. The opening may have a first length **L1** in a first direction. In addition, the first light blocking pattern **110** may form an opening corresponding to a first sub-pixel **SP1**, a second sub-pixel **SP2** and a third sub-pixel **SP3**.

The buffer layer **120** may be disposed on the base substrate **100** on which the first light blocking pattern **110** is disposed. The buffer layer **120** may prevent diffusion of metal atoms and/or impurities from the base substrate **100**. Additionally, the buffer layer **120** may adjust heat transfer rate of a successive crystallization process for an active pattern ACT, to thereby obtaining a substantially uniform active pattern ACT. In case that the base substrate **100** may have a relatively uneven surface, the buffer layer **120** may improve flatness of the surface of the base substrate **100**. The buffer layer **120** may be formed using a silicon compound. For example, the buffer layer **120** may include silicon oxide (**SiOx**), silicon nitride (**SiNx**), silicon oxynitride (**SiOxNy**), silicon oxycarbide (**SiOxCy**), silicon carbon nitride (**SiCxNy**), etc. These may be used alone or in a combination thereof. The buffer layer **120** may have a single layer structure or a multi layer structure. For example, the buffer layer **120** may have a single-layered structure including a silicon oxide film, a silicon nitride film, a silicon oxynitride film, a silicon oxycarbide film or a silicon carbon nitride film. Alternatively, the buffer layer **120** may have a multi-layered structure including at least two of a silicon oxide film, a silicon nitride film, a silicon oxynitride film, a silicon oxycarbide film, a silicon carbon nitride film, etc.

The active pattern ACT may be disposed on the buffer layer **120**. The active pattern ACT may include silicon (**Si**). In another example embodiment, the active pattern ACT may include a oxide semiconductor containing a binary compound (**ABx**), a ternary compound (**ABxCy**) and/or a quaternary compound (**ABxCyDz**). For example, the active pattern ACT may include indium (**In**), zinc (**Zn**), gallium (**Ga**), stannum (**Sn**), titanium (**Ti**), aluminum (**Al**), hafnium (**Hf**), zirconium (**Zr**) and/or magnesium (**Mg**).

The first insulation layer **130** may be disposed on the buffer layer **120** on which the active pattern ACT is disposed. The first insulation layer **130** may include a silicon compound, metal oxide, etc. For example, the first insulation layer **130** may be formed using silicon oxide (**SiOx**), silicon nitride (**SiNx**), silicon oxynitride (**SiOxNy**), aluminum oxide (**AlOx**), tantalum oxide (**TaOx**), hafnium oxide (**HfOx**), zirconium oxide (**ZrOx**), titanium oxide (**TiOx**), etc. These may be used alone or in a combination thereof. In addition, the first insulation layer **130** may have a single layer structure or a multi layer structure including the silicon oxide and/or the silicon nitride. In example embodiments, the first insulation layer **130** may be uniformly formed on the buffer layer **120** along a profile of the active pattern ACT. Here, the first insulation layer **130** may have a substantially small thickness, such that a stepped portion may be formed at a portion of the first insulation layer **130** adjacent to the active pattern ACT. In some example embodiments, the first insulation layer **130** may have a relatively large thickness for sufficiently covering the active pattern ACT, so that the first insulation layer **130** may have a substantially even surface.

The gate pattern GP may be disposed on the first insulation layer **130**. The gate pattern GP may include metal, metal alloy, conductive metal oxide, a transparent conductive

material, etc. For example, the gate pattern GP may be formed using aluminum (Al), alloy containing aluminum, aluminum nitride (AlN_x), silver (Ag), alloy containing silver, tungsten (W), tungsten nitride (WN_x), copper (Cu), alloy containing copper, nickel (Ni), alloy containing nickel, chrome (Cr), chrome nitride (CrN_x), molybdenum (Mo), alloy containing molybdenum, titanium (Ti), titanium nitride (TiN_x), platinum (Pt), tantalum (Ta), tantalum nitride (TaN_x), neodymium (Nd), scandium (Sc), strontium ruthenium oxide (SRO), zinc oxide (ZnO_x), indium tin oxide (ITO), tin oxide (SnO_x), indium oxide (InO_x), gallium oxide (GaO_x), indium zinc oxide (IZO), etc. These may be used alone or in a combination thereof. In example embodiments, the gate pattern GP may have a single layer structure or a multi layer structure, which may include a metal film, a metal alloy film, a metal nitride film, a conductive metal oxide film and/or a transparent conductive film.

The gate pattern GP may include a gate electrode GE overlapping the active pattern ACT, a signal line to transmit driving signal for pixel, and a storage electrode.

The second insulation layer **140** may be disposed on the first insulation layer **130** on which the gate pattern GP is disposed. The second insulation layer **140** may have a single-layered structure or a multi-layered structure including at least two insulation films. The second insulation layer **140** may be formed using an organic material. For example, the second insulation layer **140** may include photoresist, acryl-based resin, polyimide-based resin, polyamide-based resin, siloxane-based resin, etc. These may be used alone or in a combination thereof. Alternatively, the second insulation layer **140** may include an inorganic material. For example, the second insulation layer **140** may be formed using silicon oxide, silicon nitride, silicon oxynitride, silicon oxycarbide, aluminum oxide, titanium oxide, tantalum oxide, magnesium oxide, zinc oxide, hafnium oxide, zirconium oxide, titanium oxide, etc. These may be used alone or in a mixture thereof.

The second insulation layer **140** may have an opening corresponding to the transparent window W.

The data pattern DP may be disposed on the second insulation layer **140**. The data pattern DP may include metal, metal alloy, conductive metal oxide, a transparent conductive material, etc. For example, the gate pattern GP may be formed using aluminum (Al), alloy containing aluminum, aluminum nitride (AlN_x), silver (Ag), alloy containing silver, tungsten (W), tungsten nitride (WN_x), copper (Cu), alloy containing copper, nickel (Ni), alloy containing nickel, chrome (Cr), chrome nitride (CrN_x), molybdenum (Mo), alloy containing molybdenum, titanium (Ti), titanium nitride (TiN_x), platinum (Pt), tantalum (Ta), tantalum nitride (Ta_xN), neodymium (Nd), scandium (Sc), strontium ruthenium oxide (SRO), zinc oxide (ZnO_x), indium tin oxide (ITO), tin oxide (SnO_x), indium oxide (InO_x), gallium oxide (GaO_x), indium zinc oxide (IZO), etc. These may be used alone or in a combination thereof. In example embodiments, the data pattern DP may have a single layer structure or a multi-layer structure, which may include a metal film, a metal alloy film, a metal nitride film, a conductive metal oxide film and/or a transparent conductive film.

The data pattern DP may include source electrode SE, a drain electrode DE, a signal line to transmit driving signal for pixel and a storage electrode. The source electrode SE may be electrically connected to the active pattern ACT through a contact hole formed through the first insulation layer **130** and the second insulation layer **140**. The drain electrode DE may be electrically connected to the active

pattern ACT through a contact hole formed through the first insulation layer **130** and the second insulation layer **140**.

The active pattern ACT, the gate electrode GE, the source electrode SE and the drain electrode DE may compose the thin film transistor TFT.

The third insulation layer **150** may be disposed on the second insulation layer **140** on which the thin film transistor TFT is disposed. The third insulation layer **150** may have a single-layered structure or a multi-layered structure including at least two insulation films. The third insulation layer **150** may be formed using an organic material. For example, the third insulation layer **140** may include photoresist, acryl-based resin, polyimide-based resin, polyamide-based resin, siloxane-based resin, etc. These may be used alone or in a combination thereof. Alternatively, the third insulation layer **150** may include an inorganic material. For example, the third insulation layer **150** may be formed using silicon oxide, silicon nitride, silicon oxynitride, silicon oxycarbide, aluminum oxide, titanium oxide, tantalum oxide, magnesium oxide, zinc oxide, hafnium oxide, zirconium oxide, titanium oxide, etc. These may be used alone or in a mixture thereof.

The third insulation layer **150** may have an opening corresponding to the transparent window W.

The first electrode EL1 may be disposed on the third insulation layer **150**. The first electrode EL1 may be electrically connected to the drain electrode DE through a contact hole formed through the third insulation layer **150**.

The first electrode EL1 may include a reflective material or a transmissive material in accordance with the emission type of the display apparatus. For example, the first electrode EL1 may be formed using aluminum, alloy containing aluminum, aluminum nitride, silver, alloy containing silver, tungsten, tungsten nitride, copper, alloy containing copper, nickel, alloy containing nickel, chrome, chrome nitride, molybdenum, alloy containing molybdenum, titanium, titanium nitride, platinum, tantalum, tantalum nitride, neodymium, scandium, strontium ruthenium oxide, zinc oxide, indium tin oxide, tin oxide, indium oxide, gallium oxide, indium zinc oxide, etc. These may be used alone or in a combination thereof. In example embodiments, the first electrode EL1 may have a single layer structure or a multi-layer structure, which may include a metal film, a metal alloy film, a metal nitride film, a conductive metal oxide film and/or a transparent conductive film.

The pixel defining layer **160** may be disposed on the third insulation layer **150** on which the first electrode EL1 is disposed. The pixel defining layer **160** may include an organic material or an inorganic material. For example, the pixel defining layer **160** may be formed using photoresist, acryl-based resin, polyacryl-based resin, polyimide-based resin, a silicon compound, etc.

The pixel defining layer **160** may define an opening corresponding to the transparent window W through which external light passes, and an opening corresponding to a pixel area in which light is emitted such as a first pixel area SP1, a second sub-pixel SP2 and a third sub-pixel SP3. The pixel defining layer **160** may overlap the first light blocking pattern **110** in a plan view. The opening which corresponds to the transparent window W may have a third length L3 in the first direction.

The light emitting structure **170** may be disposed on the first electrode EL1 exposed by the opening of the pixel defining layer **160**. The light emitting structure **170** may extend on a sidewall of the opening of the pixel defining layer **160**. The light emitting structure **170** may be formed by a laser induced thermal imaging process, a printing process,

etc. The light emitting structure **170** may include an organic light emitting layer (EL), a hole injection layer (HIL), a hole transfer layer (HTL), an electron transfer layer (ETL), an electron injection layer (EIL), etc. In example embodiments, a plurality of organic light emitting layers may be formed using light emitting materials for generating different colors of light such as a red color of light (R), a green color of light (G) and a blue color of light (B) in accordance with color pixels of the display device. In some example embodiments, the organic light emitting layer of the of the light emitting structure **170** may include a plurality of stacked light emitting materials for generating a red color of light, a green color of light and a blue color of light to thereby emitting a white color of light.

The second electrode **EL2** may be disposed on the light emitting structure **170** and the pixel defining layer **160**. The second electrode **EL2** may include a transmissive material or a reflective material in accordance with the emission type of the display device. For example, the second electrode **EL2** may be formed using aluminum, alloy containing aluminum, aluminum nitride, silver, alloy containing silver, tungsten, tungsten nitride, copper, alloy containing copper, nickel, alloy containing nickel, chrome, chrome nitride, molybdenum, alloy containing molybdenum, titanium, titanium nitride, platinum, tantalum, tantalum nitride, neodymium, scandium, strontium ruthenium oxide, zinc oxide, indium tin oxide, tin oxide, indium oxide, gallium oxide, indium zinc oxide, etc. These may be used alone or in a combination thereof. In example embodiments, the second electrode **EL2** may also have a single layer structure or a multi layer structure, which may include a metal film, a metal alloy film, a metal nitride film, a conductive metal oxide film and/or a transparent conductive film.

The sealing substrate **200** may be disposed facing the base substrate **100**. The sealing substrate **200** may include transparent material and be configured to prevent ambient air and moisture from permeating into the transparent organic light emitting display apparatus. The sealing substrate **200** may be combined to the base substrate **100** to seal space between the base substrate **100** and the sealing substrate **200** by a sealing agent. A desiccant or a filler may be filled into the space **180**.

The second light blocking pattern **210** may be disposed on the sealing substrate **200**. The second light blocking pattern **210** may include organic material or inorganic material which can block the light. For example, the second light blocking pattern **210** may be a black matrix pattern including chrome. The second light blocking pattern **210** may define an opening corresponding to the first sub-pixel **SP1**, a second sub-pixel **SP2** and a third sub-pixel **SP3** and an opening corresponding to the transparent window **W**. The opening corresponding to the transparent window **W** may have a second length **L2** in the first direction.

The second length **L2** and the first length **L1** may be smaller than the third length **L3**. Thus, the opening formed through the first light blocking pattern **110** and the opening formed through the second light blocking pattern **210** may be smaller than the opening formed through the pixel defining layer **160**. The opening formed through the first light blocking pattern **110** may have substantially same shape as the opening formed through the second light blocking pattern **210**. In addition, in consideration with alignment error between the first substrate **100** and the second substrate **200**, the opening formed through the second light blocking pattern **210** may be smaller than the opening formed through the first light blocking pattern **110**. On the other hand, the opening formed through the first light

blocking pattern **110** may be smaller than the opening formed through the second light blocking pattern **210**.

A boundary of the pixel defining layer **160** may be covered by the second light blocking pattern **210** and the first light blocking pattern **110**, so that reflection of external light passing the transparent window **W** by the elements of the transparent organic light emitting display apparatus may be decreased. Thus, quality of a transmitted image by the external light may be improved.

The color filter **CF** may be disposed on the sealing substrate **200** on which the second light blocking pattern **210** is disposed. In one example embodiment, the color filter **CF** may include first to third color filters. In this case, the first color filter may be a red color filter, the second color filter may be a green color filter, and the third color filter may be a blue color filter. The first to third color filters may be disposed corresponding to the first to third sub-pixels, respectively. Each of the color filters may have a color substantially same as a luminous color of corresponding light emitting structure **170**. Accordingly, the display apparatus may have improved contrast. The color filter **CF** may be omitted depending on the light emitting portions used. For example, when the light emitting portions in the first subpixel **SP1**, the second subpixel **SP2** and the third subpixel **SP3** emit primary colors, for example, a red color, a green color and a blue color, respectively, the color filters may be omitted.

FIG. 3 is a cross-sectional view illustrating a transparent organic light emitting display apparatus according to an example embodiment of the inventive concept.

Referring to FIG. 3, the transparent organic light emitting display apparatus may be substantially same as the transparent organic light emitting display apparatus of FIG. 2, except for a first light blocking pattern and a second light blocking pattern. Thus, any further detailed descriptions concerning the same elements will be omitted.

The transparent organic light emitting display apparatus may include a base substrate **100**, a first light blocking pattern **110**, a buffer layer **120**, a thin film transistor **TFT**, a first insulation layer **130**, a gate pattern **GP**, a second insulation layer **140**, a data pattern **DP**, a third insulation layer **150**, a first electrode **EL1**, a pixel defining layer **160**, a third light blocking pattern **165**, a light emitting structure **170**, a second electrode **EL2**, a sealing substrate **200**, a second light blocking layer **210**, and a color filter **CF**.

The base substrate **100** may include a transparent insulation substrate.

The first light blocking pattern **110** may be disposed on the base substrate **100**. The first light blocking pattern **110** may block light. The first light blocking pattern **110** may include organic material or inorganic material which can block the light. For example, the first light blocking pattern **110** may be a black matrix pattern including chrome.

The first light blocking pattern **110** may define an opening corresponding to a transparent window **W**. The opening may have a first length **L1** in a first direction. The first light blocking pattern **110** may be formed to cover an area of the **TFT**, the gate pattern **GP**, the data pattern **DP** and the light emitting pattern **170** in a plan view which may be disposed on the first light blocking pattern **110**.

The buffer layer **120** may be disposed on the base substrate **100** on which the first light blocking pattern **110** is disposed.

The active pattern **ACT** may be disposed on the buffer layer **120**.

The first insulation layer **130** may be disposed on the buffer layer **120** on which the active pattern ACT is disposed.

The gate pattern GP may be disposed on the first insulation layer **130**. The gate pattern GP may include a gate electrode GE overlapping the active pattern ACT, a signal line to transmit driving signal for pixel, and a storage electrode.

The second insulation layer **140** may be disposed on the first insulation layer **130** on which the gate pattern GP is disposed.

The data pattern DP may be disposed on the second insulation layer **140**. The data pattern DP may include source electrode SE, a drain electrode DE, a signal line to transmit driving signal for pixel and a storage electrode.

The active pattern ACT, the gate electrode GE, the source electrode SE and the drain electrode DE may compose the thin film transistor TFT.

The third insulation layer **150** may be disposed on the second insulation layer **140** on which the thin film transistor TFT is disposed.

The first electrode EL1 may be disposed on the third insulation layer **150**. The first electrode EL1 may be electrically connected to the drain electrode DE through a contact hole formed through the third insulation layer **150**.

The pixel defining layer **160** may be disposed on the third insulation layer **150** on which the first electrode EL1 is disposed. The pixel defining layer **160** may include an organic material or an inorganic material. For example, the pixel defining layer **160** may be formed using photoresist, acryl-based resin, polyacryl-based resin, polyimide-based resin, a silicon compound, etc.

The pixel defining layer **160** may define an opening corresponding to the transparent window W through which external light passes, and an opening corresponding to a pixel area in which light is emitted such as a first pixel area SP1, a second sub-pixel SP2 and a third sub-pixel SP3. The pixel defining layer **160** may overlap the first light blocking pattern **110**.

The third light blocking pattern **165** may be disposed on boundary side surfaces of the opening of the pixel defining layer **160** which corresponds to the transparent window W. Thus, a side surface of the pixel defining layer **160** may be covered by the third light blocking pattern **165**. The third light blocking pattern **165** may include organic material or inorganic material which can block the light. For example, the third light blocking pattern **165** may be a black matrix pattern including chrome.

The third light blocking pattern **165** may define an opening corresponding to the transparent window W. The opening may have a third length L3 in the first direction.

The light emitting structure **170** may be disposed on the first electrode EL1 exposed by the opening of the pixel defining layer **160**. The light emitting structure **170** may extend on a sidewall of the opening of the pixel defining layer **160**. The light emitting structure **170** may be formed by a laser induced thermal imaging process, a printing process, etc. The light emitting structure **170** may include an organic light emitting layer (EL), a hole injection layer (HIL), a hole transfer layer (HTL), an electron transfer layer (ETL), an electron injection layer (EIL), etc. In example embodiments, a plurality of organic light emitting layers may be formed using light emitting materials for generating different colors of light such as a red color of light (R), a green color of light (G) and a blue color of light (B) in accordance with color pixels of the display device. In some example embodiments, the organic light emitting layer of the of the light emitting

structure **170** may include a plurality of stacked light emitting materials for generating a red color of light, a green color of light and a blue color of light to thereby emitting a white color of light.

The light emitting structure **170** may be spaced apart from the third light blocking pattern **165**. Thus, the light emitting structure **170** may not be directly contact the third light blocking pattern **165**.

The second electrode EL2 may be disposed on the light emitting structure **170** and the pixel defining layer **160**.

The sealing substrate **200** may be disposed facing the base substrate **100**. The sealing substrate **200** may be combined to the base substrate **100** to seal space between the base substrate **100** and the sealing substrate **200** by a sealing agent. A desiccant or a filler may be filled into the space **180**.

The second light blocking pattern **210** may be disposed on the sealing substrate **200**.

The second light blocking pattern **210** may include organic material or inorganic material which can block the light. For example, the second light blocking pattern **210** may be a black matrix pattern including chrome. The second light blocking pattern **210** may define an opening corresponding to the first sub-pixel SP1, a second sub-pixel SP2 and a third sub-pixel SP3 and an opening corresponding to the transparent window W. The opening corresponding to the transparent window W may have a second length L2 in the first direction.

The second length L2 and the first length L1 may be smaller than the third length L3. Thus, the opening formed through the first light blocking pattern **110** and the opening formed through the second light blocking pattern **210** may be smaller than the opening of the third light blocking pattern **165**. The opening formed through the first light blocking pattern **110** may have substantially same shape as the opening formed through the second light blocking pattern **210**. In addition, in consideration with alignment error between the first substrate **100** and the second substrate **200**, the opening formed through the second light blocking pattern **210** may be smaller than the opening formed through the first light blocking pattern **110**. On the other hand, the opening formed through the first light blocking pattern **110** may be smaller than the opening formed through the second light blocking pattern **210**.

A boundary of the pixel defining layer **160** may be covered by the second light blocking pattern **210** and the first light blocking pattern **110**, and the third light blocking pattern **165** is formed on the boundary side surfaces of the opening of the pixel defining layer **160**, so that reflection of external light passing the transparent window W by the elements of the transparent organic light emitting display apparatus may be decreased. Thus, quality of a transmitted image by the external light may be improved.

The color filter CF may be disposed on the sealing substrate **200** on which the second light blocking pattern **210** is disposed. The color filter CF may be omitted depending on the light emitting portions used. For example, when the light emitting portions in the first subpixel SP1, the second subpixel SP2 and the third subpixel SP3 emit primary colors, for example, a red color, a green color and a blue color, respectively, the color filters may be omitted.

FIG. 4 is a cross-sectional view illustrating a transparent organic light emitting display apparatus according to an example embodiment of the inventive concept.

Referring to FIG. 4, the transparent organic light emitting display apparatus may be substantially same as the transparent organic light emitting display apparatus of FIG. 2, except for a first light blocking pattern and a first insulation

layer. Thus, any further detailed descriptions concerning the same elements will be omitted.

The transparent organic light emitting display apparatus may include a base substrate **100**, a first light blocking pattern **110**, a buffer layer **120**, a thin film transistor TFT, a first insulation layer **130**, a gate pattern GP, a second insulation layer **140**, a data pattern DP, a third insulation layer **150**, a first electrode EL1, a pixel defining layer **160**, a light emitting structure **170**, a second electrode EL2, a sealing substrate **200**, a second light blocking pattern **210**, and a color filter CF.

The base substrate **100** may include a transparent insulation substrate.

The first light blocking pattern **110** may be disposed on a bottom surface of the base substrate **100**. The first light blocking pattern **110** may block light. The first light blocking pattern **110** may include organic material or inorganic material which can block the light. For example, the first light blocking pattern **110** may be a black matrix pattern including chrome.

The first light blocking pattern **110** may define an opening corresponding to a transparent window W. The opening may have a first length L1 in a first direction.

The buffer layer **120** may be disposed on a top surface of the base substrate **100**. The top surface of the base substrate **100** is opposite to the bottom surface of the base substrate **100**. Thus, the first light blocking pattern **110** may be disposed on an outer surface of the transparent organic light emitting display apparatus.

The active pattern ACT may be disposed on the buffer layer **120**.

The first insulation layer **130** may be disposed on the buffer layer **120** on which the active pattern ACT is disposed. The first insulation layer **130** may define an opening corresponding to the transparent window W.

The first insulation layer **130** may be disposed on the buffer layer **120** on which the active pattern ACT is disposed. The first insulation layer **130** may include a silicon compound, metal oxide, etc. For example, the first insulation layer **130** may be formed using silicon oxide (SiOx), silicon nitride (SiNx), silicon oxynitride (SiOxNy), aluminum oxide (AlOx), tantalum oxide (TaOx), hafnium oxide (HfOx), zirconium oxide (ZrOx), titanium oxide (TiOx), etc. These may be used alone or in a combination thereof. In addition, the first insulation layer **130** may have a single layer structure or a multi layer structure including the silicon oxide and/or the silicon nitride. In example embodiments, the first insulation layer **130** may be uniformly formed on the buffer layer **120** along a profile of the active pattern ACT. Here, the first insulation layer **130** may have a substantially small thickness, such that a stepped portion may be formed at a portion of the first insulation layer **130** adjacent to the active pattern ACT. In some example embodiments, the first insulation layer **130** may have a relatively large thickness for sufficiently covering the active pattern ACT, so that the first insulation layer **130** may have a substantially level surface.

The gate pattern GP may be disposed on the first insulation layer **130**. The gate pattern GP may include a gate electrode GE overlapping the active pattern ACT, a signal line to transmit driving signal for pixel, and a storage electrode.

The second insulation layer **140** may be disposed on the first insulation layer **130** on which the gate pattern GP is disposed. The second insulation layer **140** may define an opening corresponding to the transparent window W. The second insulation layer **140** may have substantially same shape as that of the first insulation layer **130** in a plan view.

The data pattern DP may be disposed on the second insulation layer **140**. The data pattern DP may include source electrode SE, a drain electrode DE, a signal line to transmit driving signal for pixel and a storage electrode.

The active pattern ACT, the gate electrode GE, the source electrode SE and the drain electrode DE may compose the thin film transistor TFT.

The third insulation layer **150** may be disposed on the second insulation layer **140** on which the thin film transistor TFT is disposed. The third insulation layer **150** may define an opening corresponding to the transparent window W.

The first electrode EL1 may be disposed on the third insulation layer **150**.

The pixel defining layer **160** may be disposed on the third insulation layer **150** on which the first electrode EL1 is disposed.

The pixel defining layer **160** may define an opening corresponding to the transparent window W through which external light passes. The pixel defining layer **160** may overlap the first light blocking pattern **110**. The opening corresponding to the transparent window W may have a third length L3 in the first direction.

The light emitting structure **170** may be disposed on the first electrode EL1 exposed by the opening of the pixel defining layer **160**.

The second electrode EL2 may be disposed on the light emitting structure **170** and the pixel defining layer **160**.

The sealing substrate **200** may be disposed facing the base substrate **100**. The sealing substrate **200** may be combined to the base substrate **100** and the sealing substrate **200** by a sealing agent. A desiccant or a filler may be filled into the space **180**.

The second light blocking pattern **210** may be disposed on the sealing substrate **200**.

The second light blocking pattern **210** may include organic material or inorganic material which can block the light. For example, the second light blocking pattern **210** may be a black matrix pattern including chrome. The second light blocking pattern **210** may define an opening corresponding to the first sub-pixel SP1, a second sub-pixel SP2 and a third sub-pixel SP3 and an opening corresponding to the transparent window W. The opening corresponding to the transparent window W may have a second length L2 in the first direction.

The second length L2 and the first length L1 may be smaller than the third length L3. Thus, the opening formed through the first light blocking pattern **110** and the opening formed through the second light blocking pattern **210** may be smaller than the opening formed through the pixel defining layer **160**. The opening formed through the first light blocking pattern **110** may have substantially same shape as the opening formed through the second light blocking pattern **210**. In addition, in consideration with alignment error between the first substrate **100** and the second substrate **200**, the opening formed through the second light blocking pattern **210** may be smaller than the opening formed through the first light blocking pattern **110**. On the other hand, the opening formed through the first light blocking pattern **110** may be smaller than the opening formed through the second light blocking pattern **210**.

A boundary of the pixel defining layer **160** may be covered by the second light blocking pattern **210** and the first light blocking pattern **110**, so that reflection of external light passing the transparent window W by the elements of the transparent organic light emitting display apparatus may be decreased. Thus, quality of a transmitted image by the external light may be improved.

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The color filter CF may be disposed on the sealing substrate **200** on which the second light blocking pattern **210** is disposed. The color filter CF may be omitted depending on the light emitting portions used. For example, when the light emitting portions in the first subpixel SP1, the second subpixel SP2 and the third subpixel SP3 emit primary colors, for example, a red color, a green color and a blue color, respectively, the color filters may be omitted.

FIG. 5 is a cross-sectional view illustrating a transparent organic light emitting display apparatus according to an example embodiment of the inventive concept.

Referring to FIG. 5, the transparent organic light emitting display apparatus may be substantially same as the transparent organic light emitting display apparatus of FIG. 2, except for a thin film encapsulation layer, a second light blocking pattern and a color filter. Thus, any further detailed descriptions concerning the same elements will be omitted.

The transparent organic light emitting display apparatus may include a base substrate **100**, a first light blocking pattern **110**, a buffer layer **120**, a thin film transistor TFT, a first insulation layer **130**, a gate pattern GP, a second insulation layer **140**, a data pattern DP, a third insulation layer **150**, a first electrode EL1, a pixel defining layer **160**, a light emitting structure **170**, a second electrode EL2, a thin film encapsulation (TFE) layer **190**, a color filter CF and a second light blocking layer **210**.

The base substrate **100** may include a transparent insulation substrate.

The first light blocking pattern **110** may be disposed on a bottom surface of the base substrate **100**. The first light blocking pattern **110** may define an opening corresponding to a transparent window W. The opening may have a first length L1 in a first direction. The first light blocking pattern **110** may be formed to cover an area of the TFT, the gate pattern GP, the data pattern DP and the light emitting pattern **170** in a plan view which may be disposed on the first light blocking pattern **110**.

The buffer layer **120** may be disposed on a top surface of the base substrate **100**.

The active pattern ACT may be disposed on the buffer layer **120**.

The first insulation layer **130** may be disposed on the buffer layer **120** on which the active pattern ACT is disposed. The first insulation layer **130** may define an opening corresponding to the transparent window W.

The gate pattern GP may be disposed on the first insulation layer **130**. The gate pattern GP may include a gate electrode GE overlapping the active pattern ACT, a signal line to transmit driving signal for pixel, and a storage electrode.

The second insulation layer **140** may be disposed on the first insulation layer **130** on which the gate pattern GP is disposed. The second insulation layer **140** may define an opening corresponding to the transparent window W. The second insulation layer **140** may have substantially same shape as that of the first insulation layer **130** in a plan view.

The data pattern DP may be disposed on the second insulation layer **140**. The data pattern DP may include source electrode SE, a drain electrode DE, a signal line to transmit driving signal for pixel and a storage electrode.

The active pattern ACT, the gate electrode GE, the source electrode SE and the drain electrode DE may compose the thin film transistor TFT.

The third insulation layer **150** may be disposed on the second insulation layer **140** on which the thin film transistor TFT is disposed. The third insulation layer **150** may define an opening corresponding to the transparent window W.

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The first electrode EL1 may be disposed on the third insulation layer **150**.

The pixel defining layer **160** may be disposed on the third insulation layer **150** on which the first electrode EL1 is disposed.

The pixel defining layer **160** may define an opening corresponding to the transparent window W through which external light passes. The pixel defining layer **160** may overlap the first light blocking pattern **110**. The opening corresponding to the transparent window W may have a third length L3 in the first direction.

The light emitting structure **170** may be disposed on the first electrode EL1 exposed by the opening of the pixel defining layer **160**.

The second electrode EL2 may be disposed on the light emitting structure **170** and the pixel defining layer **160**.

The TFE layer **190** may be disposed on the buffer layer **120**, the pixel defining layer **160** and the second electrode EL2. The TFE layer **190** may define an opening corresponding to the transparent window W. In one example embodiment, the TFE layer **190** may entirely cover the base substrate **100**.

The TFE layer **190** may protect the second electrode EL2 and the light emitting structure **170** by preventing ambient air and moisture from permeating into the transparent organic light emitting display apparatus. The TFE layer **190** may include an inorganic film such as silicon oxide or silicon nitride film and an organic film such as epoxy or polyimide film which are alternately and repeatedly disposed. However, example embodiments of TFE layer **190** may be not limited thereto, any structure of transparent thin film for sealing may be applied.

The color filter CF may be disposed on the TFE layer **190** on which the second light blocking pattern **210** is disposed.

In one example embodiment, the color filter CF may include first to third color filters. In this case, the first color filter may be a red color filter, the second color filter may be a green color filter, and the third color filter may be a blue color filter. The first to third color filters may be disposed corresponding to the first to third sub-pixels, respectively. Each of the color filters may have a color substantially same as a luminous color of corresponding light emitting structure **170**. Accordingly, the display apparatus may have improved contrast. The color filters CFs may be omitted depending on the light emitting portions used. For example, when the light emitting portions in the first subpixel SP1, the second subpixel SP2 and the third subpixel SP3 emit primary colors, for example, a red color, a green color and a blue color, respectively, the color filters may be omitted.

The second light blocking pattern **210** may be disposed on the buffer layer **120**, the TFE layer **190** and the color filter CF. The second light blocking pattern **210** may include organic material or inorganic material which can block the light. For example, the second light blocking pattern **210** may be a black matrix pattern including chrome. The second light blocking pattern **210** may define an opening corresponding to the first sub-pixel SP1, a second sub-pixel SP2 and a third sub-pixel SP3 and an opening corresponding to the transparent window W. The opening corresponding to the transparent window W may have a second length L2 in the first direction.

The second length L2 and the first length L1 may be smaller than the third length L3. Thus, the opening formed through the first light blocking pattern **110** and the opening formed through the second light blocking pattern **210** may be smaller than the opening formed through the pixel defining layer **160**. The opening formed through the first

light blocking pattern **110** may have substantially same shape as the opening formed through the second light blocking pattern **210**. In addition, in consideration with alignment error between the first substrate **100** and the second substrate **200**, the opening formed through the second light blocking pattern **210** may be smaller than the opening formed through the first light blocking pattern **110**. On the other hand, the opening formed through the first light blocking pattern **110** may be smaller than the opening formed through the second light blocking pattern **210**.

A boundary of the pixel defining layer **160** may be covered by the second light blocking pattern **210** and the first light blocking pattern **110**, so that reflection of external light passing the transparent window **W** by the elements of the transparent organic light emitting display apparatus may be decreased. Thus, quality of a transmitted image by the external light may be improved.

FIGS. **6A** to **6J** are cross-sectional views illustrating a method of manufacturing the transparent organic light emitting display apparatus of FIG. **2**.

Referring to FIG. **6A**, a first light blocking layer **110** may be formed on a base substrate **100**.

The base substrate **100** may include a transparent insulation substrate. For example, the base substrate **100** may include a glass substrate, a quartz substrate, a transparent resin substrate, etc. Examples of the transparent resin substrate for the base substrate **100** may include polyimide-based resin, acryl-based resin, polyacrylate-based resin, polycarbonate-based resin, polyether-based resin, sulfonic acid containing resin, polyethyleneterephthalate-based resin, etc.

The first light blocking pattern **110** may include material which can block light. The first light blocking pattern **110** may include organic material or inorganic material which can block light. For example, the first light blocking pattern **110** may be a black matrix pattern including chrome.

The first light blocking pattern **110** may define an opening corresponding to a transparent window (refers to **W** of FIG. **6J**). The opening may have a first length **L1** in a first direction. In addition, the first light blocking pattern **110** may form an opening corresponding to a first sub-pixel (refers to **SP1** of FIG. **6J**).

Referring to FIG. **6B**, a buffer layer **120** may be formed on the base substrate **100** on which the first light blocking pattern **110** is formed. The buffer layer **120** may be formed by a spin coating process, a chemical vapor deposition (CVD) process, a plasma enhanced chemical vapor deposition (PECVD) process, a high density plasma-chemical vapor deposition (HDP-CVD) process, a printing process, etc.

And then, an active pattern **ACT** may be formed on the buffer layer **120**.

A semiconductor layer (not illustrated) may be formed on the buffer layer **120**, and then a preliminary active layer (not illustrated) may be formed on the buffer layer **120** by patterning the semiconductor layer. The crystallization process may be performed to crystallize the preliminary active layer to form the active pattern **ACT** on the buffer layer **120**. Here, the semiconductor layer may be formed by a CVD process, a PECVD process, a low pressure chemical vapor deposition (LPCVD) process, a sputtering process, a printing process, etc. When the semiconductor layer includes amorphous silicon, the active pattern **ACT** may include polysilicon. The crystallization process for forming the active pattern **ACT** may include a laser irradiation process, a thermal treatment process, a thermal process utilizing a catalyst, etc. In some example embodiments, a dehydrogenation process may be performed about the semiconductor

layer and/or the preliminary active layer after forming the semiconductor layer and/or the preliminary active layer on the buffer layer **120**. The dehydrogenation process may reduce the hydrogen concentration of the semiconductor layer and/or the preliminary active layer, so that the active pattern **ACT** may have improved electrical characteristics.

Referring to FIG. **6C**, a first insulation layer **130** may be formed on the buffer layer **120** on which the active pattern **ACT** is formed.

The first insulation layer **130** may be formed by a CVD process, a spin coating process, a PECVD process, a sputtering process, a vacuum evaporation process, an HDP-CVD process, a printing process, etc.

And then, a gate pattern **GP** may be formed on the first insulation layer **130**. In example embodiments, a conductive layer (not illustrated) may be formed on the first insulation layer **130**, and then the conductive layer may be patterned by a photolithography process. Hence, the gate pattern **GP** may be provided on the first insulation layer **130**. The conductive layer may be formed by a printing process, a sputtering process, a CVD process, a pulsed laser deposition (PLD) process, a vacuum evaporation process, an atomic layer deposition (ALD) process, etc. When the conductive layer is formed by a printing process, the photolithography process may be omitted.

The gate pattern **GP** may include a gate electrode **GE** overlapping the active pattern **ACT**, a signal line to transmit driving signal for pixel, and a storage electrode.

Referring to FIG. **6D**, a second insulation layer **140** may be formed on the first insulation layer **130** on which the gate pattern **GP** is formed. The second insulation layer **140** may be formed by a CVD process, a spin coating process, a PECVD process, a sputtering process, a vacuum evaporation process, an HDP-CVD process, a printing process, etc.

A first contact hole **CNT1** and a second contact hole **CNT2** exposing the active pattern **ACT** may be formed by partially etching the second insulation layer **140** and the first insulation layer **130**. The first contact hole **CNT1** may expose a portion of the active pattern **ACT**. For example, the first contact hole **CNT1** may expose a source area of the active pattern. The second contact hole **CNT2** may expose a portion of the active pattern **ACT**. For example, the second contact hole **CNT2** may expose a drain area of the active pattern.

In addition, the second insulation layer **140** may have an opening corresponding to the transparent window **W**.

Referring to FIG. **6E**, a data pattern **DP** may be formed on the second insulation layer **140**. In example embodiments, a conductive layer (not illustrated) may be formed on the second insulation layer **140**, and then the conductive layer may be patterned by a photolithography process. Hence, the data pattern **DP** may be provided on the second insulation layer **140**. The conductive layer may be formed by a printing process, a sputtering process, a CVD process, a PLD process, a vacuum evaporation process, an ALD process, etc. When the conductive layer is formed by a printing process, the photolithography process may be omitted.

The data pattern **DP** may include source electrode **SE**, a drain electrode **DE**, a signal line to transmit driving signal for pixel and a storage electrode. The source electrode **SE** may be electrically connected to the active pattern **ACT** through the first contact hole **CNT1**. The drain electrode **DE** may be electrically connected to the active pattern **ACT** through the second contact hole **CNT2**.

The active pattern **ACT**, the gate electrode **GE**, the source electrode **SE** and the drain electrode **DE** may compose the thin film transistor **TFT**.

Referring to FIG. 6F, a third insulation layer **150** may be formed on the second insulation layer **140** on which the thin film transistor TFT is formed. In example embodiments, a planarization process may be executed on the third insulation layer **150** to enhance the flatness of the third insulation layer **150**. For example, the third insulation layer **150** may have a substantially even surface by a chemical mechanical polishing (CMP) process, an etch-back process, etc. The third insulation layer **50** may be formed using an organic material.

The third insulation layer **150** may be obtained by a spin coating process, a printing process, a sputtering process, a CVD process, an ALD process, a PECVD process, an HDP-CVD process or a vacuum evaporation process in accordance with ingredients included in the third insulation layer **150**.

A third contact hole CNT3 may be formed by partially etching the third insulation layer **150** to expose the drain electrode DE.

In addition, the third insulation layer **150** may have an opening corresponding to the transparent window W.

And then, a first electrode EL1 may be formed on the third insulation layer **150**. In example embodiments, a conductive layer (not illustrated) may be formed on the third insulation layer **150**, and then the conductive layer may be patterned by a photolithography process. Hence, the first electrode EL1 may be provided on the third insulation layer **150**. The conductive layer may be formed by a printing process, a sputtering process, a CVD process, a PLD process, a vacuum evaporation process, an ALD process, etc. When the conductive layer is formed by a printing process, the photolithography process may be omitted.

The first electrode EL1 may be electrically connected to the drain electrode DE through the third contact hole CNT3.

Referring to FIG. 6G a pixel defining layer **160** may be formed on the third insulation layer **150** on which the first electrode EL1 is formed.

The pixel defining layer **160** may be obtained by a spin coating process, a spray process, a printing process, a CVD process, etc.

The pixel defining layer **160** may define an opening corresponding to the transparent window W through which external light passes, and an opening corresponding to a pixel area in which light is emitted such as a first pixel area SP1, a second sub-pixel SP2 and a third sub-pixel SP3. The opening which corresponds to the transparent window W may have a third length L3 in the first direction.

The first length L1 may be smaller than the third length L3 by a first gap G1 and a second gap G2. Thus, the third length L3 may be longer than the first length L1 by the first gap G1 and the second gap G2 in both sides. The first gap G1 may be substantially same as the second gap G2. Each of the first gap G1 and the second gap G2 may be about 1 μm to about 5 μm .

Referring to FIG. 6H, a light emitting structure **170** is formed on the first electrode EL1 exposed by the opening of the pixel defining layer **160**. The light emitting structure **170** may be formed by a laser induced thermal imaging process, a printing process, etc.

The second electrode EL2 may be formed on the light emitting structure **170** and the pixel defining layer **160**. The second electrode EL2 may be formed by a printing process, a sputtering process, a CVD process, a PLD process, a vacuum evaporation process, an ALD process, etc.

Referring to FIG. 6I, a sealing substrate **200** may be provided. The sealing substrate **200** may include transparent material and be configured to prevent ambient air and

moisture from permeating into the transparent organic light emitting display apparatus. For example, the sealing substrate **200** may include a glass substrate, a quartz substrate, a transparent resin substrate, etc. Examples of the transparent resin substrate for the sealing substrate **200** may include polyimide-based resin, acryl-based resin, polyacrylate-based resin, polycarbonate-based resin, polyether-based resin, sulfonic acid containing resin, polyethyleneterephthalate-based resin, etc.

A second light blocking pattern **210** may be formed on the sealing substrate **200**. The second light blocking pattern **210** may include organic material or inorganic material which can block light. For example, the second light blocking pattern **210** may be a black matrix pattern including chrome. The second light blocking pattern **210** may define an opening corresponding to the first sub-pixel SP1, a second sub-pixel SP2 and a third sub-pixel SP3 and an opening corresponding to the transparent window W. The opening corresponding to the transparent window W may have a second length L2 in the first direction.

A color filter CF may be formed on the sealing substrate **200** on which the second light blocking pattern **210** is disposed. In one example embodiment, the color filter CF may include first to third color filters. In this case, the first color filter may be a red color filter, the second color filter may be a green color filter, and the third color filter may be a blue color filter. The first to third color filters may be disposed corresponding to the first to third sub-pixels, respectively. Each of the color filters may have a color substantially same as a luminous color of corresponding light emitting structure **170**. Accordingly, the display apparatus may have improved contrast.

Referring to FIG. 6J, the sealing substrate **200** on which the color filter CF is formed may be combined to the base substrate **100** on which the second electrode EL2 is formed to seal space between the base substrate **100** and the sealing substrate **200** by a sealing agent. A desiccant or a filler may be filled into the space **180**.

FIGS. 7A to 7E are cross-sectional views illustrating a method of manufacturing the transparent organic light emitting display apparatus of FIG. 3.

Referring to FIG. 7A, a first light blocking pattern **110** may be formed on the base substrate **100**. The first light blocking pattern **110** may define an opening corresponding to a transparent window (refers to W of FIG. 6J). The opening may have a first length L1 in a first direction.

Referring to FIG. 7B, a buffer layer **120** may be formed on the base substrate **100** on which the first light blocking pattern **110** is formed. An active pattern ACT may be formed on the buffer layer **120**. A first insulation layer **130** may be formed on the buffer layer **120** on which the active pattern ACT is formed. A gate pattern GP including a gate electrode GE may be formed on the first insulation layer **130**. A second insulation layer **140** may be formed on the first insulation layer **130** on which the gate pattern GP is formed. Contact holes exposing the active pattern ACT may be formed by partially etching the second insulation layer **140** and the first insulation layer **130**.

And then, a data pattern DP having a source electrode SE and a drain electrode DE may be formed on the insulation layer **140**. The active pattern ACT, the gate electrode GE, the source electrode SE and the drain electrode DE may compose the thin film transistor TFT. A third insulation layer **150** may be formed on the second insulation layer **140** on which the thin film transistor TFT is formed. A contact hole exposing the drain electrode may be formed by partially etching the third insulation layer **150**.

And then, a first electrode EL1 may be formed on the third insulation layer 150. The first electrode EL1 may be electrically connected to the drain electrode DE through the contact hole formed through the third insulation layer 150. A pixel defining layer 160 may be formed on the third insulation layer 150 on which the first electrode EL1 is formed.

The pixel defining layer 160 may define an opening corresponding to the transparent window W through which external light passes, and an opening corresponding to a pixel area in which light is emitted such as a first pixel area SP1, a second sub-pixel SP2 and a third sub-pixel SP3. The opening which corresponds to the transparent window W may have a third length L3 in the first direction.

Referring to FIG. 7C, A third light blocking pattern 165 may be formed on boundary side surfaces of the opening of the pixel defining layer 160 which corresponds to the transparent window W. Thus, a side surface of the pixel defining layer 160 may be covered by the third light blocking pattern 165.

The third light blocking pattern 165 may include material which can block light. The third light blocking pattern 165 may include organic material or inorganic material which can block the light. For example, a metal layer may be formed on the pixel defining layer 160, and the metal layer may be patterned into the third light blocking pattern 165. For example, the third light blocking pattern 165 may be a black matrix pattern including chrome.

Referring to FIG. 7D, a light emitting structure 170 is formed on the first electrode EL1 exposed by the opening of the pixel defining layer 160. The light emitting structure 170 may be spaced apart from the third light blocking pattern 165. A second electrode EL2 may be formed on the pixel defining layer 160 and the light emitting structure 170.

Referring to FIG. 7E, a sealing substrate 200 may be provided. A second light blocking pattern 210 may be formed on the sealing substrate 200. A color filter CF may be formed on the sealing substrate 200 on which the second light blocking pattern 210 is disposed. The sealing substrate 200 on which the color filter CF is formed may be combined to the base substrate 100 on which the second electrode EL2 is formed to seal space between the base substrate 100 and the sealing substrate 200 by a sealing agent. A desiccant or a filler may be filled into the space 180.

FIGS. 8A to 8D are cross-sectional views illustrating a method of manufacturing the transparent organic light emitting display apparatus of FIG. 4.

Referring to FIG. 8A, a buffer layer 120 may be formed on a base substrate 100. An active pattern ACT may be formed on the buffer layer 120. A first insulation layer 130 may be formed on the buffer layer 120 on which the active pattern ACT is formed. A gate pattern GP including a gate electrode GE may be formed on the first insulation layer 130. A second insulation layer 140 may be formed on the first insulation layer 130 on which the gate pattern GP is formed.

Referring to FIG. 8B, contact holes to expose the active pattern ACT may be formed by removing a portion of the first and second insulation layers 130 and 140. A portion of the buffer layer 120 where corresponding to a transparent window (refers to W of FIG. 8C) may be exposed by removing a portion of the first and second insulation layers 130 and 140. The first and second insulation layers 130 and 140 may be partially removed at the same time.

And then, a data pattern DP having a source electrode SE and a drain electrode DE may be formed on the second insulation layer 140. The source and drain electrodes SE and

DE may be electrically connected to the active pattern ACT through the contact holes formed through the first and second insulation layers. The active pattern ACT, the gate electrode GE, the source electrode SE and the drain electrode DE may compose the thin film transistor TFT.

Referring to FIG. 8C, a third insulation layer 150 may be formed on the second insulation layer 140 on which the thin film transistor TFT is formed. A first electrode EL1 may be formed on the third insulation layer 150. A pixel defining layer 160 may be formed on the third insulation layer 150 on which the first electrode EL1 is formed.

The pixel defining layer 160 may define an opening corresponding to the transparent window W through which external light passes, and an opening corresponding to a pixel area in which light is emitted such as a first pixel area SP1, a second sub-pixel SP2 and a third sub-pixel SP3. The opening which corresponds to the transparent window W may have a third length L3 in the first direction.

A light emitting structure 170 is formed on the first electrode EL1 exposed by the opening of the pixel defining layer 160. A second electrode EL2 may be formed on the pixel defining layer 160 and the light emitting structure 170.

A second light blocking pattern 210 may be formed on a sealing substrate 200. The second light blocking pattern 210 may define an opening corresponding to the first sub-pixel SP1, a second sub-pixel SP2 and a third sub-pixel SP3 and an opening corresponding to the transparent window W. The opening corresponding to the transparent window W may have a second length L2 in the first direction.

A color filter CF may be formed on the sealing substrate 200 on which the second light blocking pattern 210 is disposed.

The sealing substrate 200 on which the color filter CF is formed may be combined to the base substrate 100 on which the second electrode EL2 is formed to seal space between the base substrate 100 and the sealing substrate 200 by a sealing agent. A desiccant or a filler may be filled into the space 180.

Referring to FIG. 8D, a first light blocking pattern 110 may be formed on an outer surface of the base substrate 100. Thus, the first light blocking pattern 110 may be formed on an opposite to the buffer layer 120 with respect to the base substrate 100. The first light blocking pattern 110 may include organic material or inorganic material which can block the light. For example, the first light blocking pattern 110 may be a black matrix pattern including chrome. In addition, the first light blocking pattern 110 may be a light blocking film attached on the base substrate 100.

FIGS. 9A and 9B are cross-sectional views illustrating another method of manufacturing the transparent organic light emitting display apparatus of FIG. 4.

The method may be substantially same as the method of FIGS. 8A to 8D except manufacturing order of a first light blocking pattern. Thus, any further detailed descriptions concerning the same elements will be omitted.

Referring to FIG. 9A, a first light blocking pattern 110 may be formed on an outer surface of the base substrate 100. For example, the first light blocking pattern 110 may be a black matrix pattern including chrome. In addition, the first light blocking pattern 110 may be a light blocking film attached on the base substrate 100.

Referring to FIG. 9B, a buffer layer 120 may be formed on a base substrate 100. The buffer layer 120 may be formed opposite to the first light blocking pattern 110 with respect to the base substrate 100. And then, an active pattern ACT, a first insulation layer 130, a gate pattern GP, a second insulation layer 140, a data pattern DP, a third insulation

layer **150**, a pixel defining layer **160**, a light emitting structure **170**, and a second electrode **EL2** may be formed. A second light blocking pattern **210** and a color filter CF may be formed on a sealing substrate **200**. The sealing substrate **200** on which the color filter CF is formed may be combined to the base substrate **100** on which the second electrode **EL2** is formed to seal space between the base substrate **100** and the sealing substrate **200** by a sealing agent.

FIGS. **10A** to **10D** are cross-sectional views illustrating a method of manufacturing the transparent organic light emitting display apparatus of FIG. **5**.

Referring to FIG. **10A**, a buffer layer **120** may be formed on the base substrate **100**. An active pattern ACT may be formed on the buffer layer **120**. A first insulation layer **130** may be formed on the buffer layer **120** on which the active pattern ACT is formed. A gate pattern GP including a gate electrode GE may be formed on the first insulation layer **130**. A second insulation layer **140** may be formed on the first insulation layer **130** on which the gate pattern GP is formed.

Referring to FIG. **10b**, contact holes to expose the active pattern ACT may be formed by removing a portion of the first and second insulation layers **130** and **140**. A portion of the buffer layer **120** where corresponding to a transparent window (refers to W of FIG. **8C**) may be exposed by removing a portion of the first and second insulation layers **130** and **140**.

And then, a data pattern DP having a source electrode SE and a drain electrode DE may be formed on the second insulation layer **140**. The source and drain electrodes SE and DE may be electrically connected to the active pattern ACT through the contact holes formed through the first and second insulation layers. The active pattern ACT, the gate electrode GE, the source electrode SE and the drain electrode DE may compose the thin film transistor TFT.

Referring to FIG. **10C**, a third insulation layer **150** may be formed on the second insulation layer **140** on which the thin film transistor TFT is formed. A first electrode **EL1** may be formed on the third insulation layer **150**. A pixel defining layer **160** may be formed on the third insulation layer **150** on which the first electrode **EL1** is formed.

The pixel defining layer **160** may define an opening corresponding to the transparent window W through which external light passes, and an opening corresponding to a pixel area in which light is emitted such as a first pixel area SP1, a second sub-pixel SP2 and a third sub-pixel SP3. The opening which corresponds to the transparent window W may have a third length L3 in the first direction.

A light emitting structure **170** is formed on the first electrode **EL1** exposed by the opening of the pixel defining layer **160**. A second electrode **EL2** may be formed on the pixel defining layer **160** and the light emitting structure **170**.

A TFE layer **190** may be disposed on the buffer layer **120**, the pixel defining layer **160** and the second electrode **EL2**. The TFE layer **190** may include an inorganic film such as silicon oxide or silicon nitride film and an organic film such as epoxy or polyimide films which are alternately and repeatedly formed. However, example embodiments of TFE layer **190** may be not limited thereto, any structure of transparent thin film for sealing may be applied.

The TFE layer **190** may define an opening corresponding to the transparent window W. In one example embodiment, the TFE layer **190** may entirely cover the base substrate **100**.

Referring to FIG. **10D**, a color filter CF may be formed on the TFE layer **190**. The second light blocking pattern **210** may be formed on the buffer layer **120**, the TFE layer **190**

and the color filter CF. The second light blocking pattern **210** may define an opening corresponding to the first sub-pixel SP1, a second sub-pixel SP2 and a third sub-pixel SP3 and an opening corresponding to the transparent window W. The opening corresponding to the transparent window W may have a second length L2 in the first direction.

Referring to FIG. **10E**, a first light blocking pattern **110** may be formed on an outer surface of the base substrate **100**. Thus, the first light blocking pattern **110** may be formed on an opposite to buffer layer **120** with respect to the base substrate **100**. The first light blocking pattern **110** may include organic material or inorganic material which can block the light. For example, the first light blocking pattern **110** may be a black matrix pattern including chrome. In addition, the first light blocking pattern **110** may be a light blocking film attached on the base substrate **100**.

According to present example embodiments, a transparent organic light emitting display apparatus may include a pixel defining layer, a first light blocking pattern and a second light blocking pattern. A boundary of the pixel defining layer may be covered by the first light blocking pattern and the second light blocking pattern, so that reflection of external light passing a transparent window by elements of the transparent organic light emitting display apparatus may be decreased. Thus, quality of a transmitted image by the external light may be improved.

In addition, the transparent organic light emitting display apparatus may include a third light blocking pattern disposed on boundary side surfaces of an opening of the pixel defining layer which corresponds to the transparent window. Reflection of external light passing the transparent window by the elements of the transparent organic light emitting display apparatus may be decreased by the first to third light blocking patterns. Thus, quality of a transmitted image by the external light may be improved.

The present inventive concept may be applied to an organic light emitting display device, and an electronic device having the organic light emitting display device. For example, the present inventive concept may be applied to a computer monitor, a television, a laptop, a digital camera, a cellular phone, a smart-phone, a smart-pad, a personal digital assistants (PDA), a portable multimedia player (PMP), an MP3 player, a navigation system, a video-phone, etc.

The foregoing is illustrative of the inventive concept and is not to be construed as limiting thereof. Although a few example embodiments of the inventive concept have been described, those skilled in the art will readily appreciate that many modifications are possible in the example embodiments without materially departing from the novel teachings and advantages of the inventive concept. Accordingly, all such modifications are intended to be included within the scope of the inventive concept as defined in the claims. In the claims, means-plus-function clauses are intended to cover the structures described herein as performing the recited function and not only structural equivalents but also equivalent structures. Therefore, it is to be understood that the foregoing is illustrative of the inventive concept and is not to be construed as limited to the specific example embodiments disclosed, and that modifications to the disclosed example embodiments, as well as other example embodiments, are intended to be included within the scope of the appended claims. The inventive concept is defined by the following claims, with equivalents of the claims to be included therein.

What is claimed is:

1. A transparent organic light emitting display apparatus comprising:

- a base substrate;
- a first light blocking pattern disposed on the base substrate;
- a thin film transistor disposed on the base substrate;
- a first electrode disposed on the base substrate and electrically connected to the thin film transistor;
- a pixel defining layer disposed on the base substrate and overlapping the first light blocking pattern;
- a second electrode disposed on the base substrate;
- a light emitting structure disposed between the first electrode and the second electrode; and
- a second light blocking pattern overlapping the first light blocking pattern,

wherein the first light blocking pattern defines a first opening, the second light blocking pattern defines a second opening which overlaps the first opening, and the pixel defining layer defines a third opening which overlaps the first and second openings configured to pass external light through the first to third openings, and

wherein a width of the second opening is smaller than a width of the third opening.

2. The transparent organic light emitting display apparatus of claim 1, wherein a width of the first opening is smaller than a width of the third opening.

3. The transparent organic light emitting display apparatus of claim 1, wherein a width of the first opening is substantially same as the width of the second opening.

4. The transparent organic light emitting display apparatus of claim 1, wherein a gap between a boundary of the first opening and a boundary of the third opening is about 1 μm to about 5 μm in a plan view, and

a gap between a boundary of the second opening and a boundary of the third opening is about 1 μm to about 5 μm in a plan view.

5. The transparent organic light emitting display apparatus of claim 4, wherein the gap between the boundary of the first opening and the boundary of the third opening is uniform.

6. The transparent organic light emitting display apparatus of claim 1, wherein the first light blocking pattern is disposed opposite to the thin film transistor with respect to the base substrate.

7. The transparent organic light emitting display apparatus of claim 1, further comprising a third light blocking pattern disposed on the pixel defining layer and spaced apart from the light emitting structure,

wherein the third light blocking pattern defines a fourth opening which covers a boundary of the third opening and overlaps the first and second openings.

8. The transparent organic light emitting display apparatus of claim 7, wherein a width of the first opening is smaller than a width of the fourth opening, and the width of the second opening is smaller than a width of the fourth opening.

9. The transparent organic light emitting display apparatus of claim 1, further comprising a color filter disposed on the second electrode,

wherein the second light blocking pattern makes contact with the color filter.

10. The transparent organic light emitting display apparatus of claim 9, further comprising a sealing substrate disposed on the color filter and the second light blocking pattern.

11. The transparent organic light emitting display apparatus of claim 1, further comprising a buffer layer covering the base substrate,

wherein the buffer layer is disposed between the base substrate and the thin film transistor, and the first light blocking pattern is disposed between the buffer layer and the base substrate.

12. The transparent organic light emitting display apparatus of claim 11, further comprising a first insulation layer disposed on the buffer layer and a second insulation layer disposed on the first insulation layer,

wherein the first and second insulation layers define an opening where the first to third openings are overlapped each other.

13. The transparent organic light emitting display apparatus of claim 12, further comprising:

a thin film encapsulation layer comprising a plurality of organic films and inorganic films which are alternately stacked;

a color filter disposed on the thin film encapsulation layer and overlapping the light emitting structure, and wherein the second light blocking pattern is disposed on the thin film encapsulation layer and configured to expose the color filter.

14. The transparent organic light emitting display apparatus of claim 1, wherein the first light blocking pattern makes contact with the base substrate.

15. A method of manufacturing a transparent organic light emitting display apparatus comprising:

forming a first light blocking pattern on a base substrate;

forming a thin film transistor on the base substrate;

forming a pixel defining layer on the base substrate on which the thin film transistor is formed;

forming a light emitting structure on the base substrate on which the pixel defining layer is formed; and

forming a second light blocking pattern overlapping the pixel defining layer, and

wherein the first light blocking pattern defines a first opening, the second light blocking pattern defines a second opening which overlaps the first opening, the pixel defining layer defines a third opening which overlaps the first and second openings, and the first to third openings are configured to pass external light therethrough, and

wherein a width of the second opening is smaller than a width of the third opening.

16. The method of claim 15, further comprising forming a third light blocking pattern on the pixel defining layer before forming the light emitting structure,

wherein the third light blocking pattern is spaced apart from the light emitting structure.

17. The method of claim 15, further comprising forming a color filter overlapping the light emitting structure before forming the second light blocking pattern.

18. The method of claim 15, further comprising forming a buffer layer on the base substrate on which the first light blocking pattern is formed before forming the thin film transistor.

19. The method of claim 15, wherein the first light blocking pattern is formed by attaching a light blocking film on the base substrate.

20. A transparent organic light emitting display apparatus comprising a transparent window configured to pass external light therethrough and a pixel configured to display an image, the transparent organic light emitting display apparatus comprising:

a first light blocking pattern defining a first opening
corresponding to the transparent window;
a second light blocking pattern overlapping the first light
blocking pattern; and
an opaque elements disposed between the first light 5
blocking pattern and the second light blocking pattern,
and
wherein the second light blocking pattern defines a second
opening overlapping the first opening, the opaque ele-
ments define a third opening overlapping the first 10
opening and the second opening, and
wherein the third opening is substantially larger than the
first opening and the second opening.

* * * * *

专利名称(译)	透明有机发光显示装置及其制造方法		
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申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
当前申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
[标]发明人	CHANG YOUNG JIN KIM MU GYEOM		
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摘要(译)

一种透明有机发光显示装置，包括：基底，设置在基底上的遮光图案，设置在基底上的薄膜晶体管，设置在基底上并电连接到薄膜晶体管的第一电极，像素限定层设置在基底基板上并与第一光阻挡图案重叠，第二电极设置在基底基板上，发光结构设置在第一电极和第二电极之间，第二光阻挡图案与第一光阻挡重叠模式。第一光阻挡图案限定第一开口。第二光阻挡图案限定了与第一开口重叠的第二开口。像素限定层限定第三开口，第三开口与第一开口和第二开口重叠，第一开口和第二开口被配置为使外部光通过第一至第三开口。

